

The SiPM readout plane for the ePIC-dRICH detector at the EIC: overview and beam test results

Nicola Rubini⁽¹⁾

on behalf of the dRICH collaboration

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17 September 2025

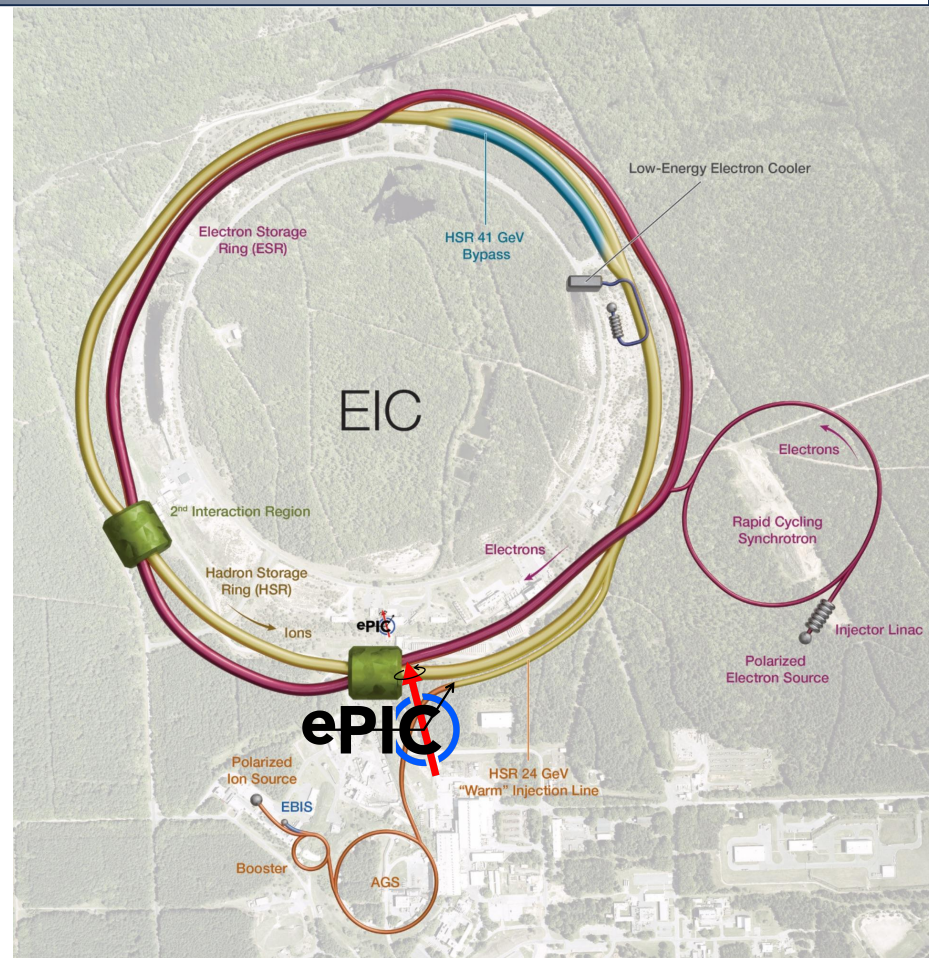
ePIC experiment at EIC

Major US project in nuclear physics, one of the most important future facilities in the field

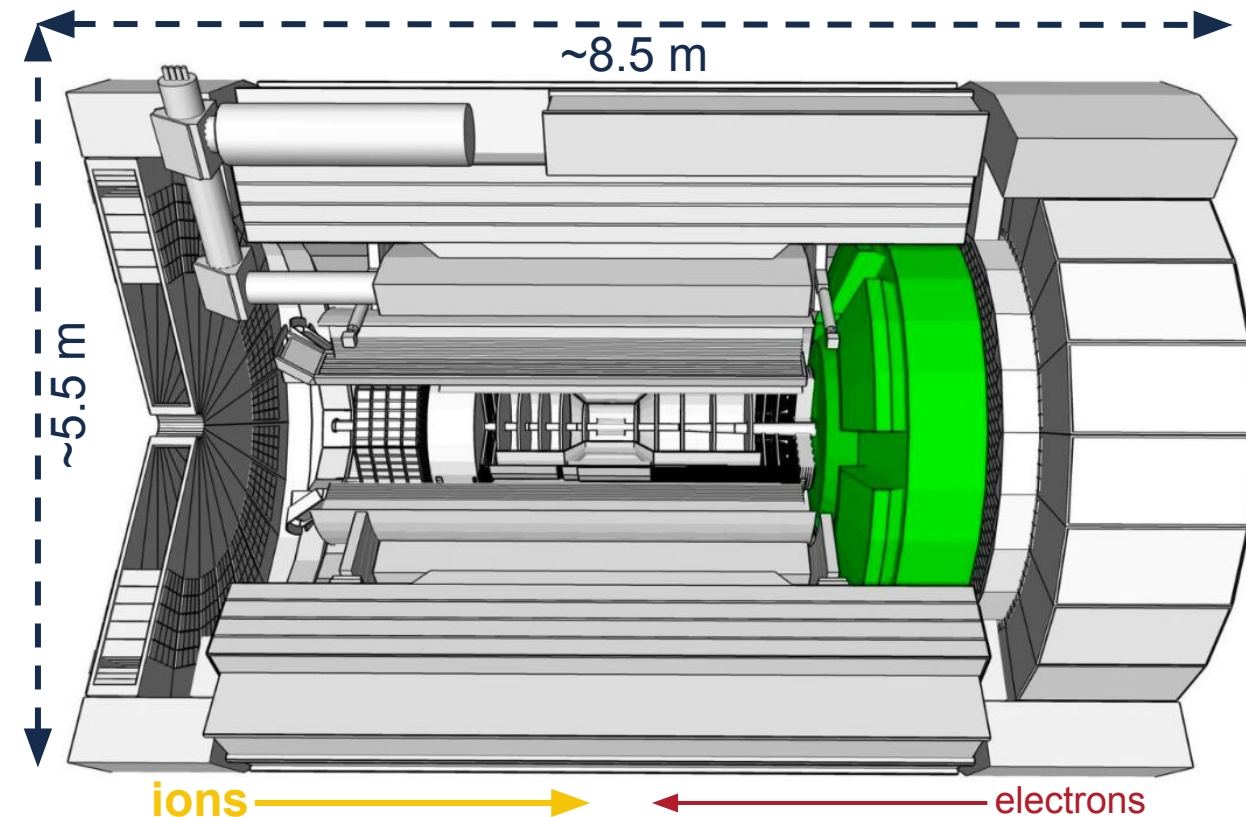
- Collision of e^- and ions from proton to uranium
- Center-of-mass energy from 20 to 140 GeV
- Highly polarised beams: $\sim 70\%$
- High luminosity $10^{33} \text{ cm}^{-2} \text{ s}^{-1}$
- One foreseen experiment: ePIC
- Start of operations in the early 2030s

Physics goals:

- Precise measurements in non-perturbative QCD
- Origin of mass & spin of the nucleons
- 3D imaging of the nuclear structure



ePIC detector layout



Tracking:

1.7 T magnet
Si-MAPS + MPGDs

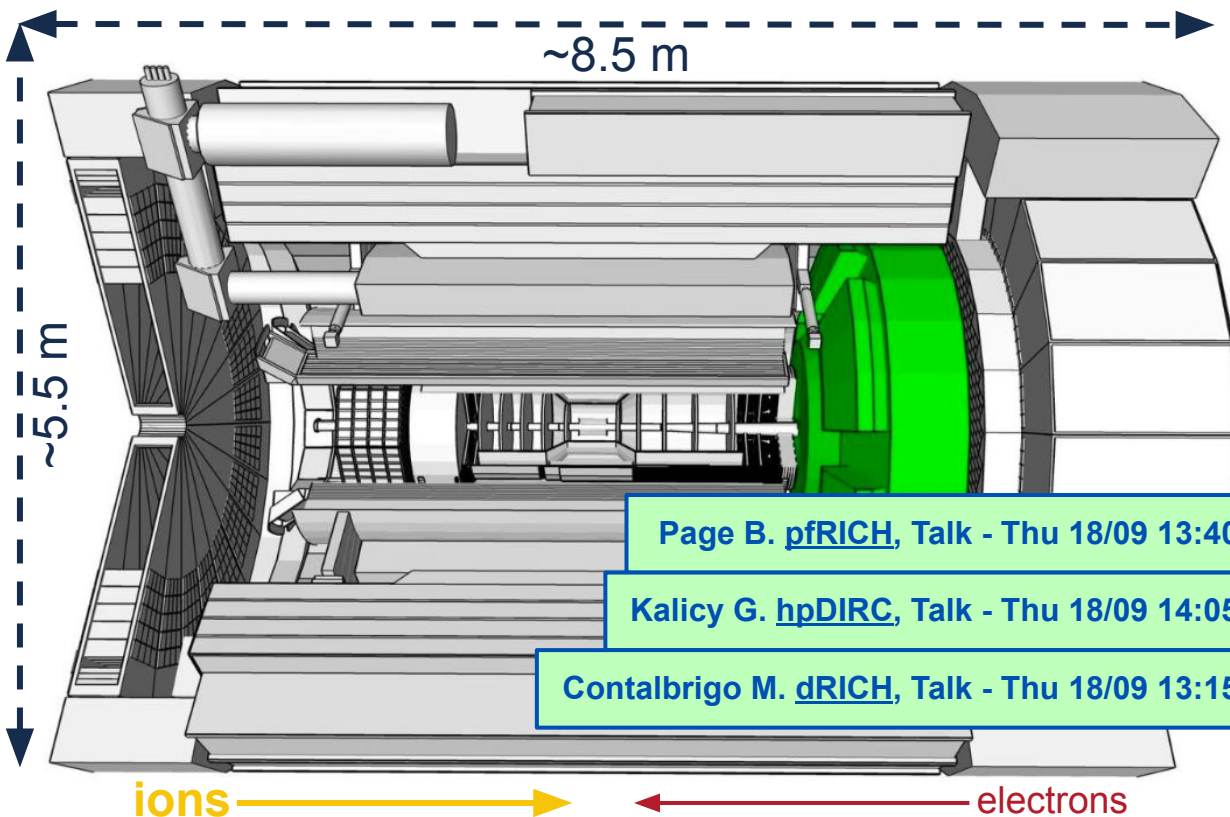
Calorimetry:

e-endcap: PbWO_4 EMCal
barrel: imaging EMCal
outer barrel: HCal
h-endcap: finely segmented

PID:

AC-LGAD TOF
pfRICH
hpDIRC
dRICH

ePIC detector layout



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Page B. [pfRICH](#), Talk - Thu 18/09 13:40

Kalicy G. [hpDIRC](#), Talk - Thu 18/09 14:05

Contalbrigo M. [dRICH](#), Talk - Thu 18/09 13:15

The dual-radiator (dRICH) for forward PID at ePIC

PID

$p \sim 3\text{-}50 \text{ GeV}/c$

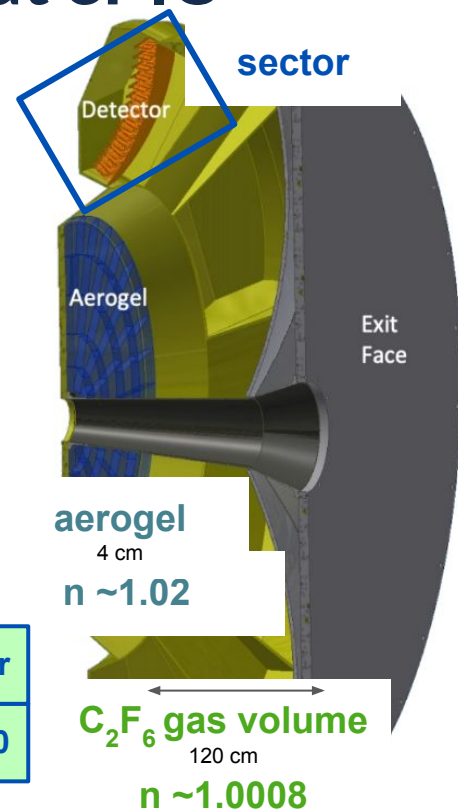
$\eta \sim 1.5\text{-}3.5$

$e \sim \text{up to } 15 \text{ GeV}/c$

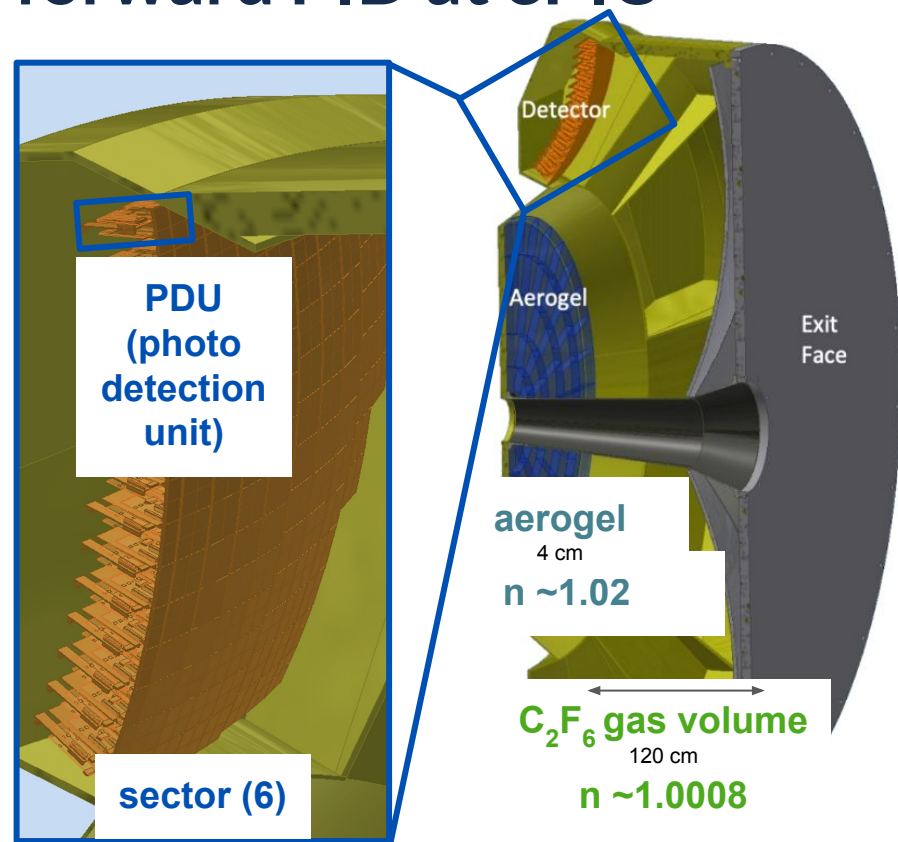
Broad momentum
coverage thanks to
two radiators

Boasso T. dRICH Performance Simulation, Poster

Tessarotto F. dRICH radiator gas, Talk - Fri 19/09 09:10



The dual-radiator (dRICH) for forward PID at ePIC



The dual-radiator (dRICH) for forward PID at ePIC

Photosensors:

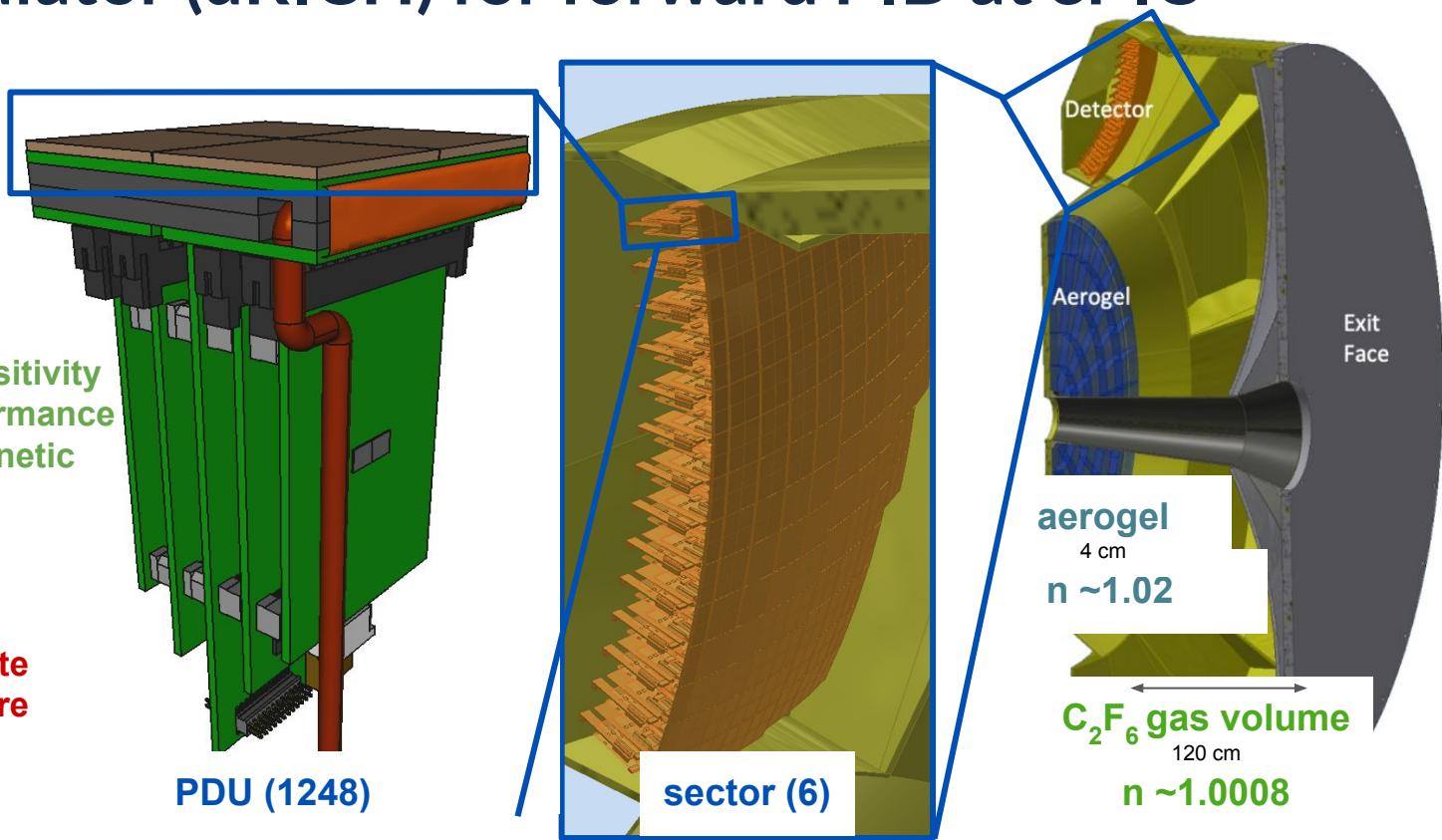
- 3x3 mm² pixels
- 0.5 m² per sector
- SiPM chosen

Pros

1. Single photon sensitivity
2. Good timing performance
3. Insensitive to magnetic fields
4. Cheap

Cons

1. High dark count rate at room temperature
2. High radiation sensitivity



The dual-radiator (dRICH) for forward PID at ePIC

Ripoli C. SiPM radiation hardness, Poster

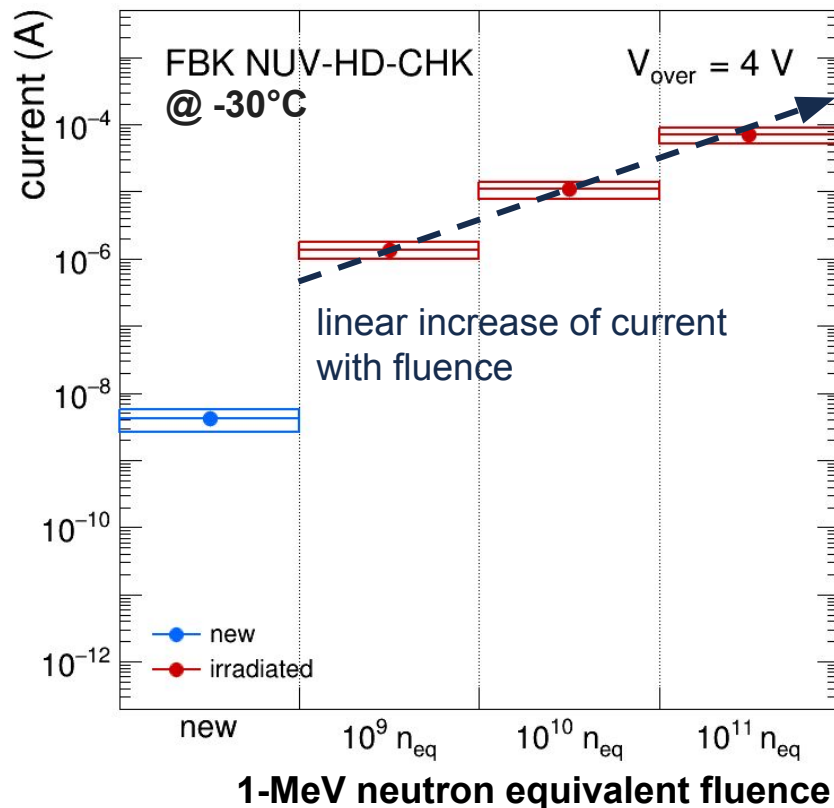
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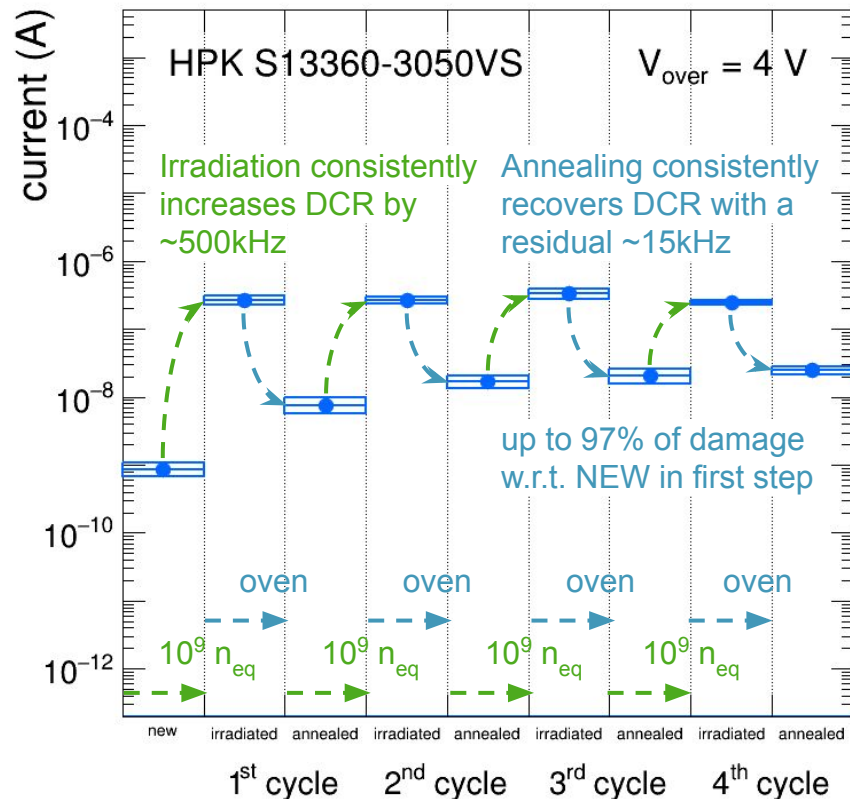
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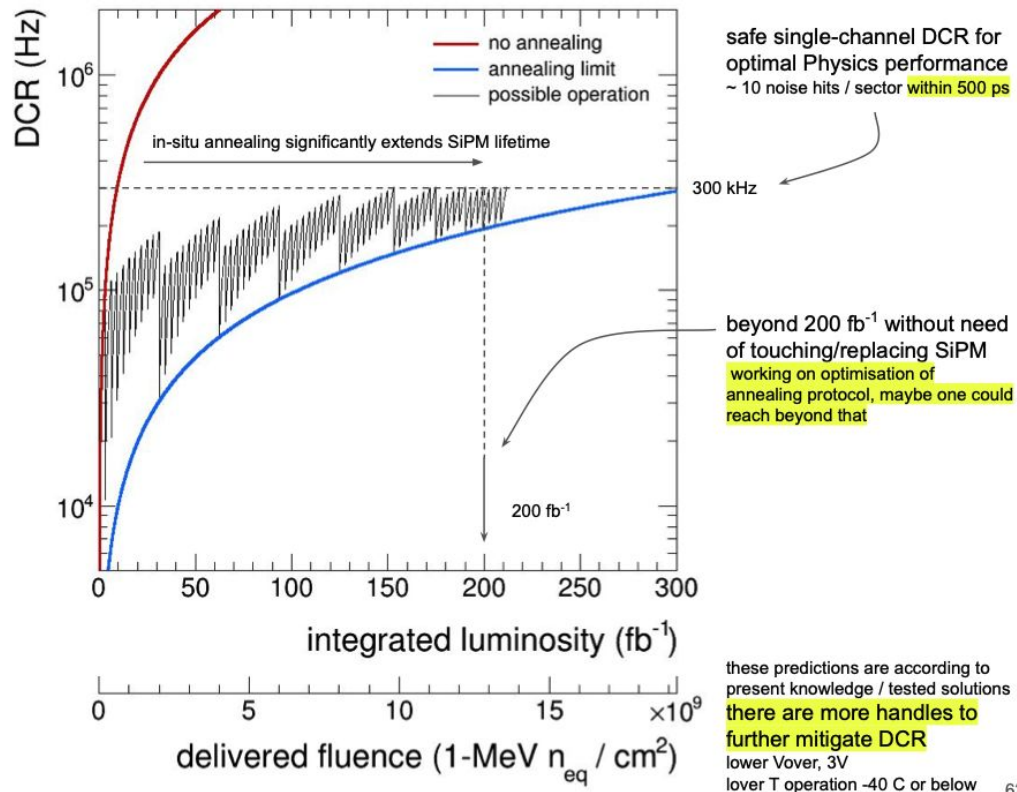
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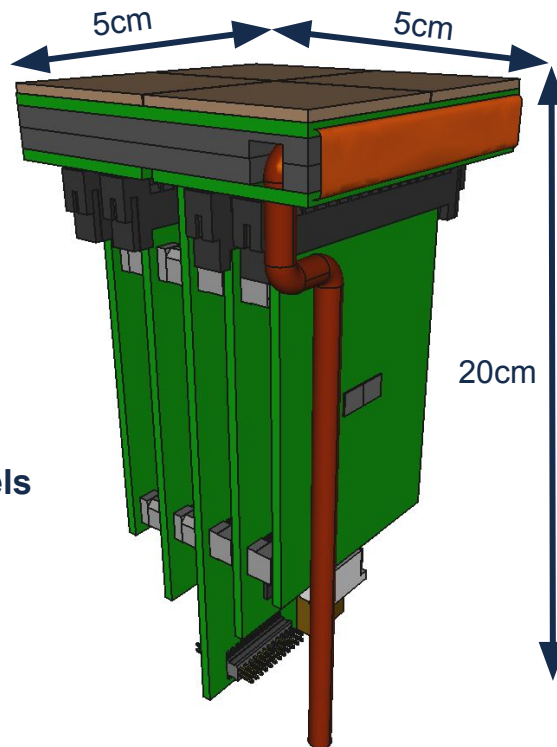
The dRICH Photo Detection Unit (PDU)

Photosensors:

- $3 \times 3 \text{ mm}^2$ pixels
- 0.5 m^2 per sector
- SiPM chosen

Specifics

1. Each PDU holds 4 matrices
2. Each matrix is 8×8 sensors
3. Total of 256 channels



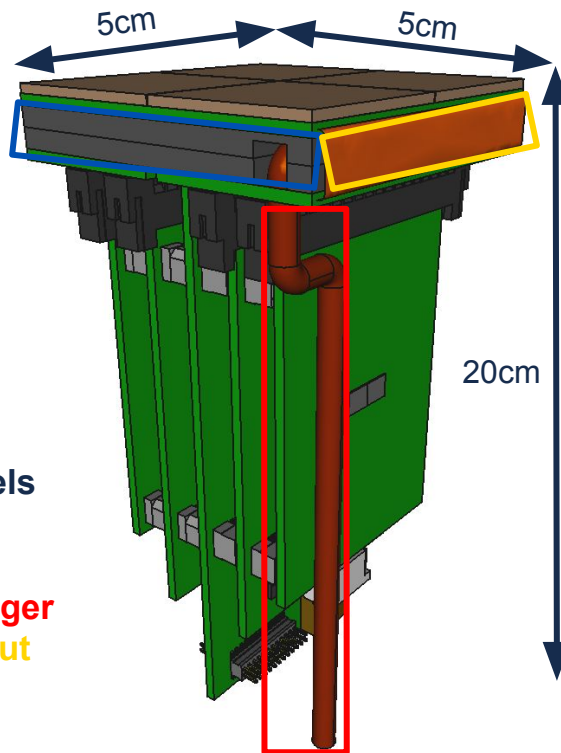
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4. Cold plate / heat exchanger
5. Liquid heat exchanger
6. Flex PCB for readout



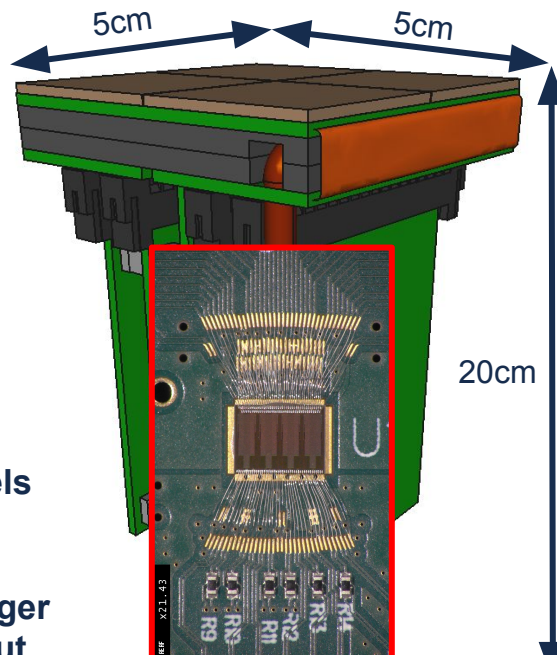
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developed by INFN Torino, 64-channel mixed signal

The chip takes care of:

- Signal amplification
- Conditioning and event digitisation

Each pixel features:

- 2 leading-edge discriminators
- 4 TDCs w/ analog interpolation
 - 20 or 40ps LSB @394MHz
- Digital shutter to allow TDC digitisation
 - Suppress out-of-gate DCR hits
 - 2-3ns timing window
 - programmable delay, sub ns accuracy

Single photon time-tagging mode:

- continuous readout
- possible time-over-threshold mode

Fully digital output:

- 8LVDS TX Data Links

Preghenella R. ALCOR chip, Poster

Rossi C. dRICH Data Reduction, Talk - Tue 16/09 15:05

The PDU prototype

4x matrices of 8x8 SiPMs
3x3 mm², total 256 channels

2 peltier cells for subzero
operating temperatures

Temperature sensors both
under the sensors and on
the peltiers

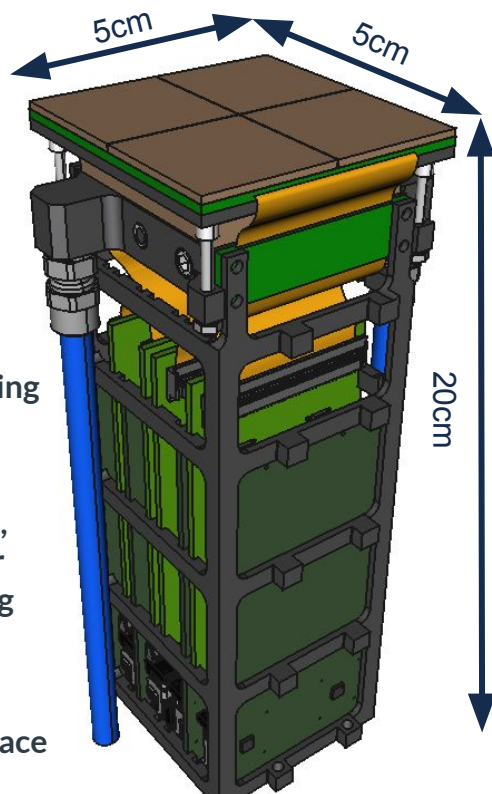
light-weight aluminium
structure

Front-end electronics featuring
the ALCOR ASIC chip

Externally provided:

High voltage bias for sensors,
low voltage power supply for
electronics, T sensors piloting
and read-out

liquid heat exchange for
temperature control of hot-face
of peltiers

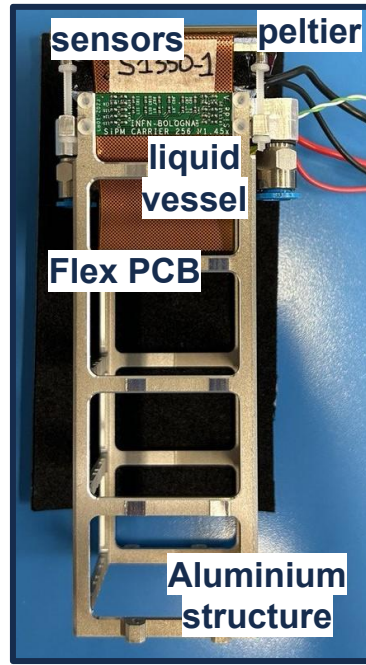
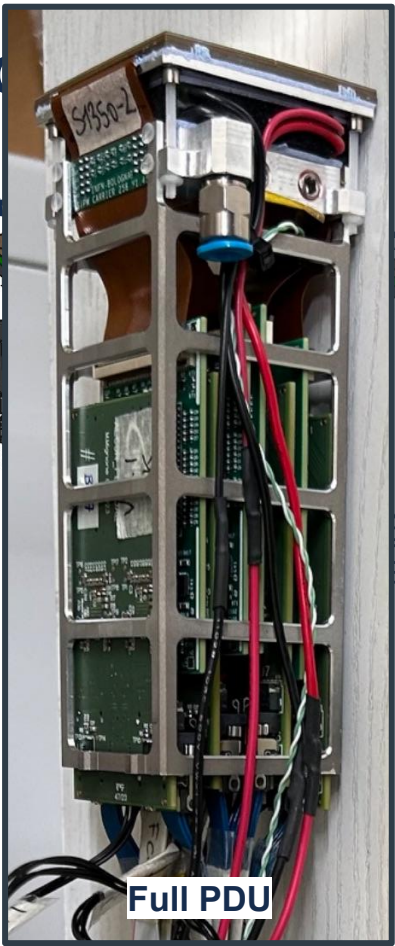


The PDU proto

4x matrices of 8x8 SiPMs
 3x3 channels
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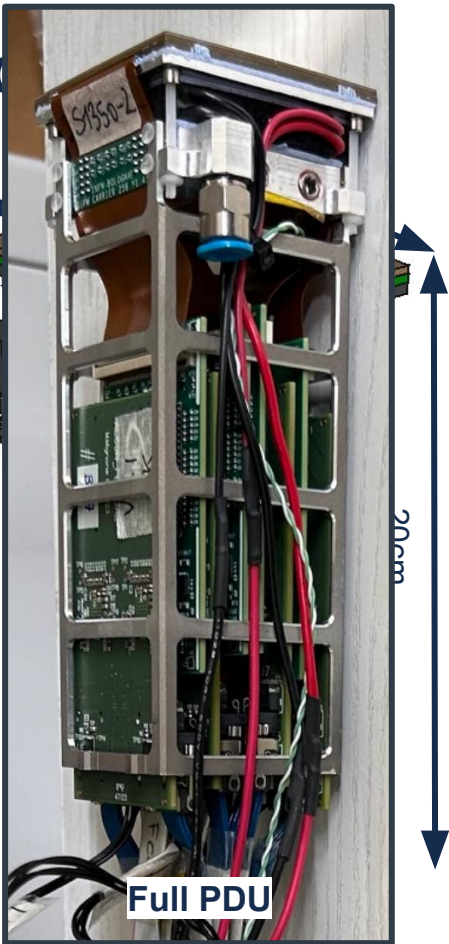
...sensors,
 ...y for
 ...oting

...not-face



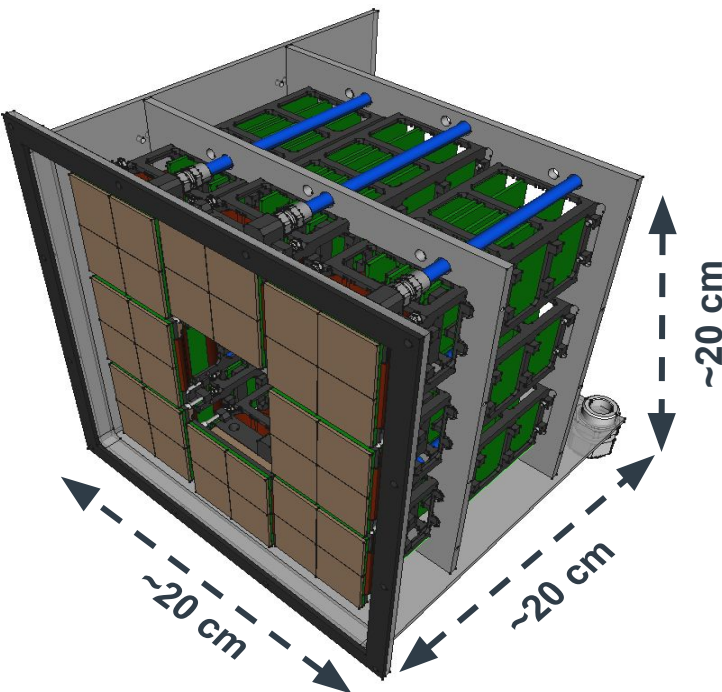
The PDU prototype

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3x3 mm², total 256 channels
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operating temperatures
- Temperature sensors both
under the sensors and on
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- light-weight aluminium
structure
- Front-end electronics featuring
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High voltage bias for sensors,
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- liquid heat exchange for
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of peltiers



Detector prototype

Compact solution for a ~18 cm² of active area, reading 2048 channels



The PDU prototype

4x matrices of 8x8 SiPMs
3x3 mm², total 256 channels

2 peltier cells for subzero
operating temperatures

Temperature sensors both
under the sensors and on
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light-weight aluminium
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Front-end electronics featuring
the ALCOR ASIC chip

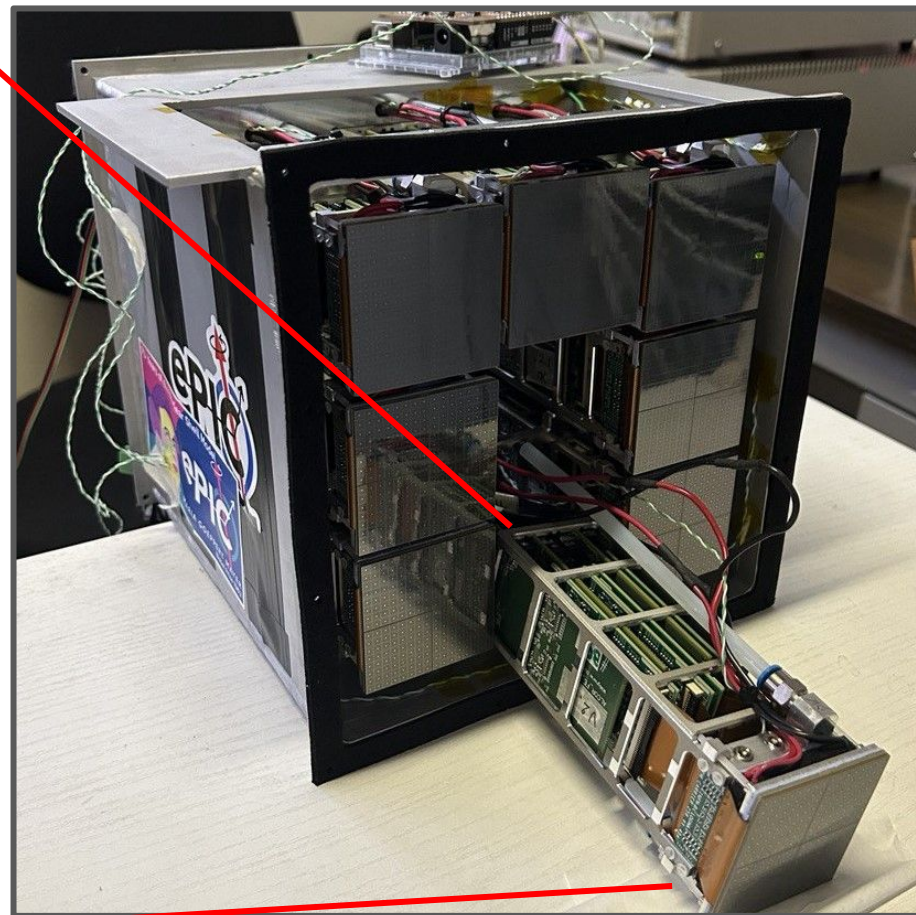
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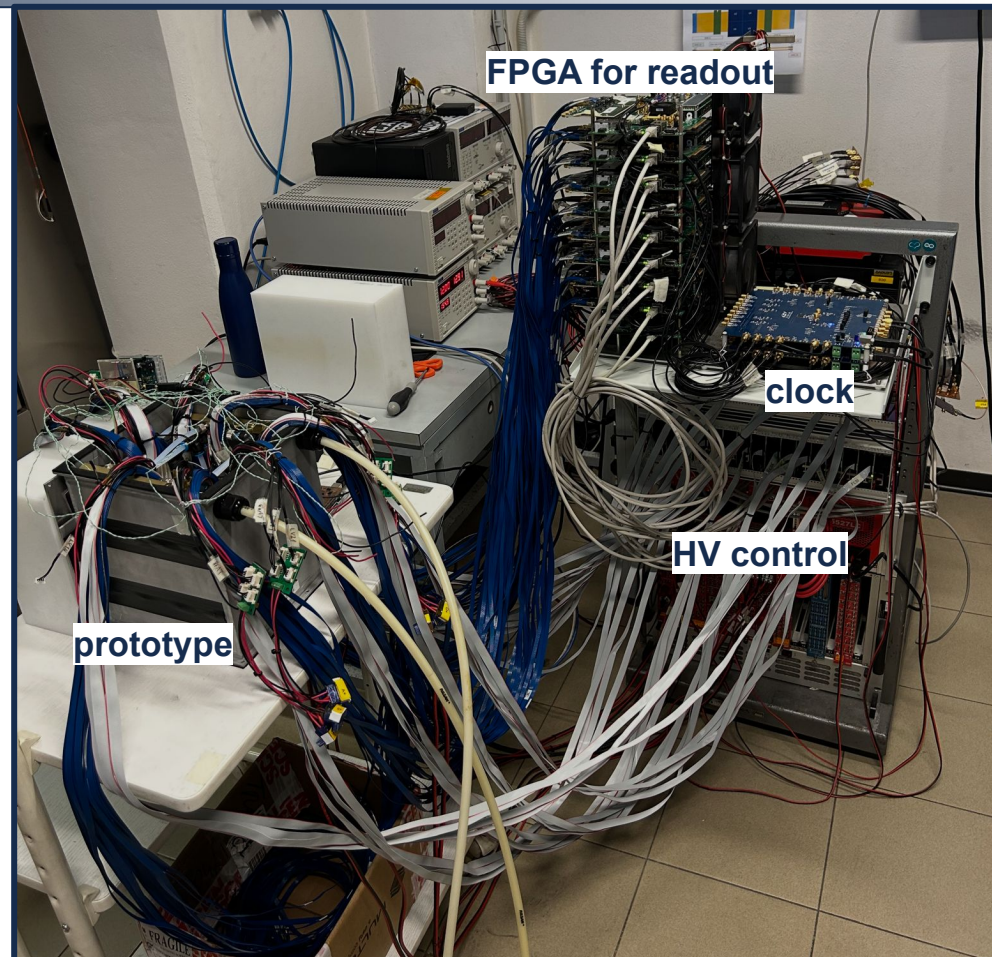
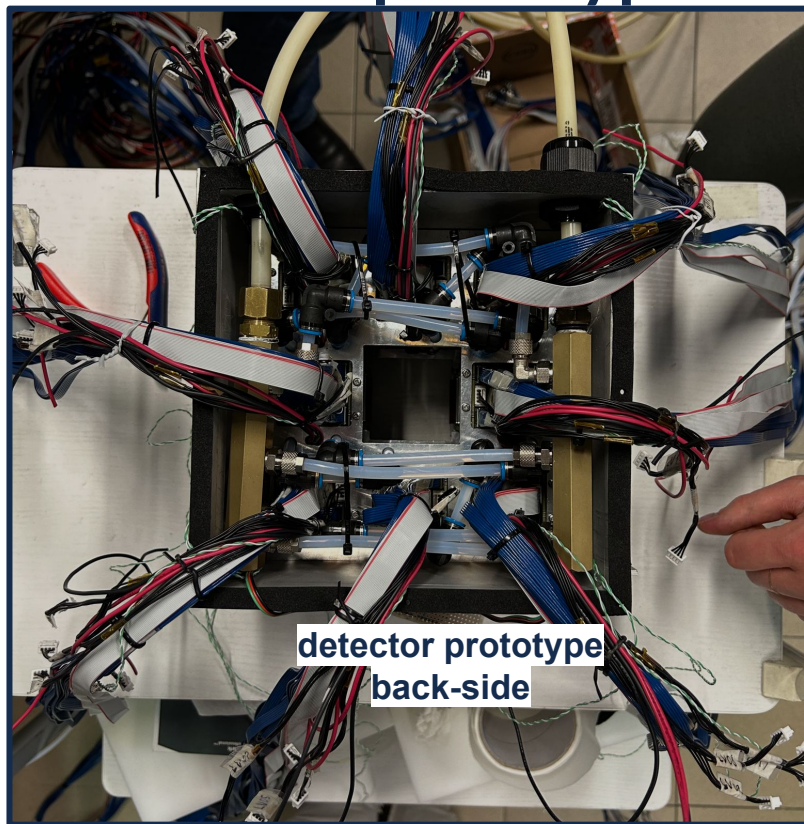
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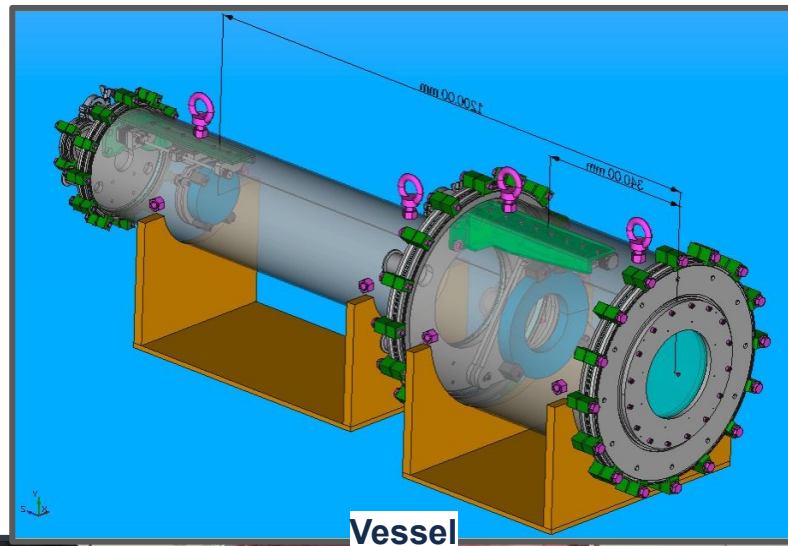
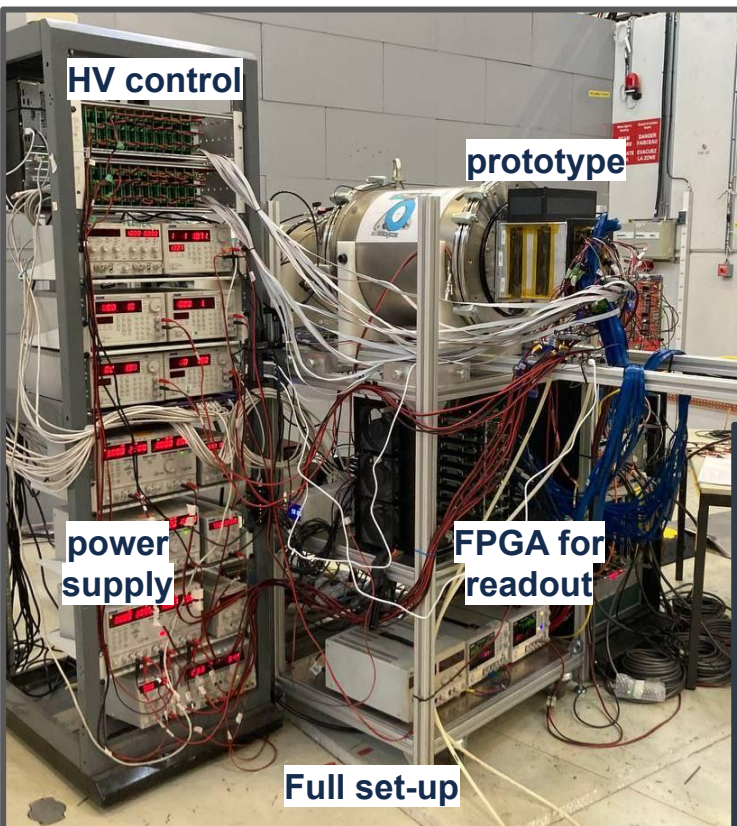
20cm



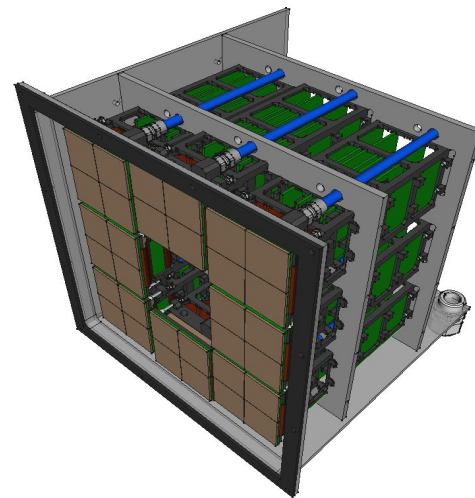
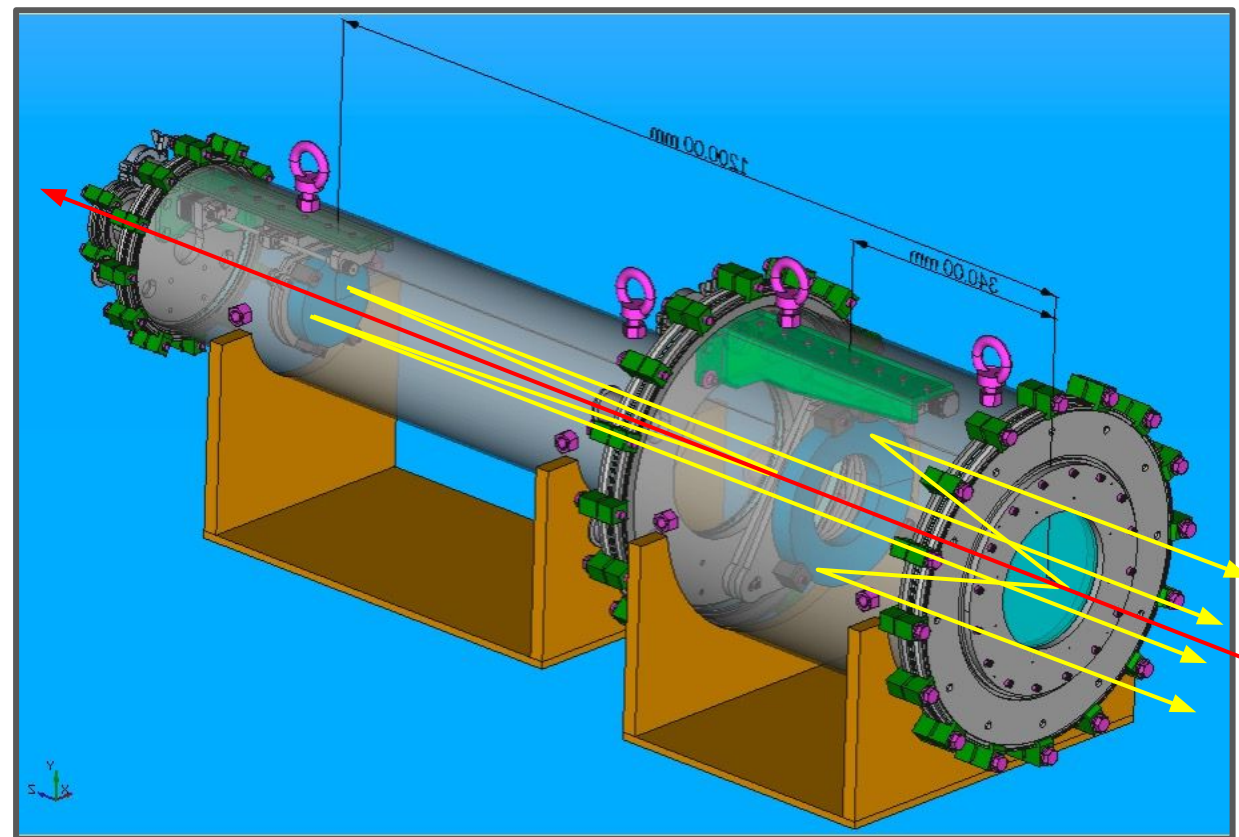
The dRICH prototype



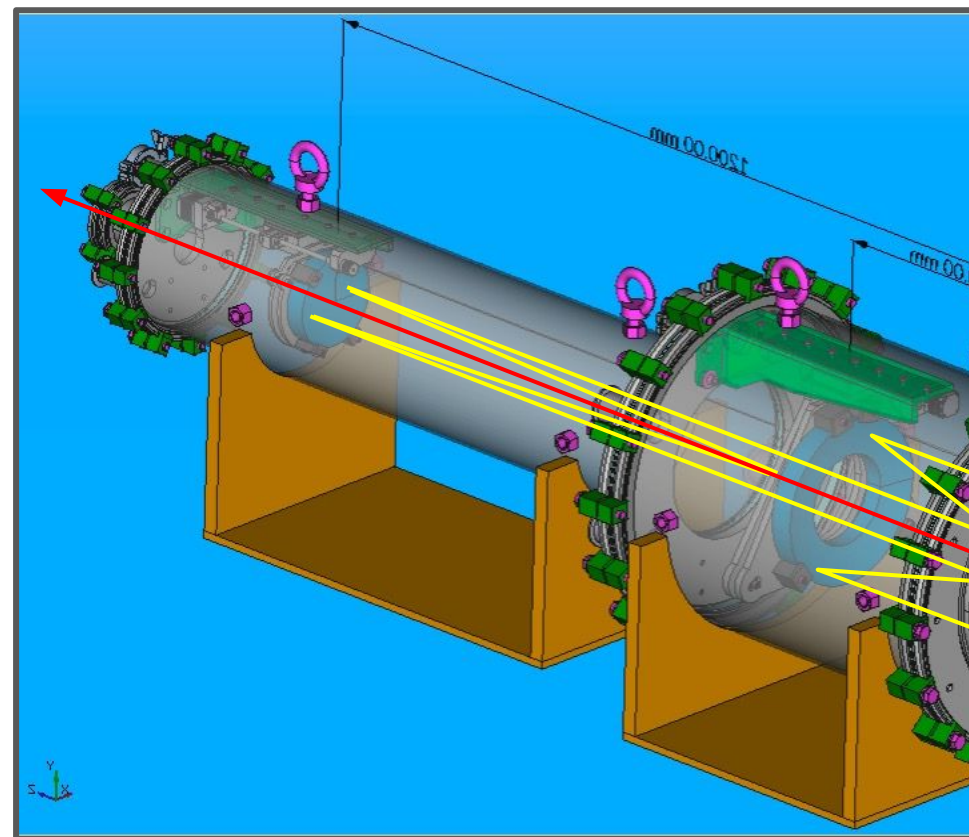
Beam test



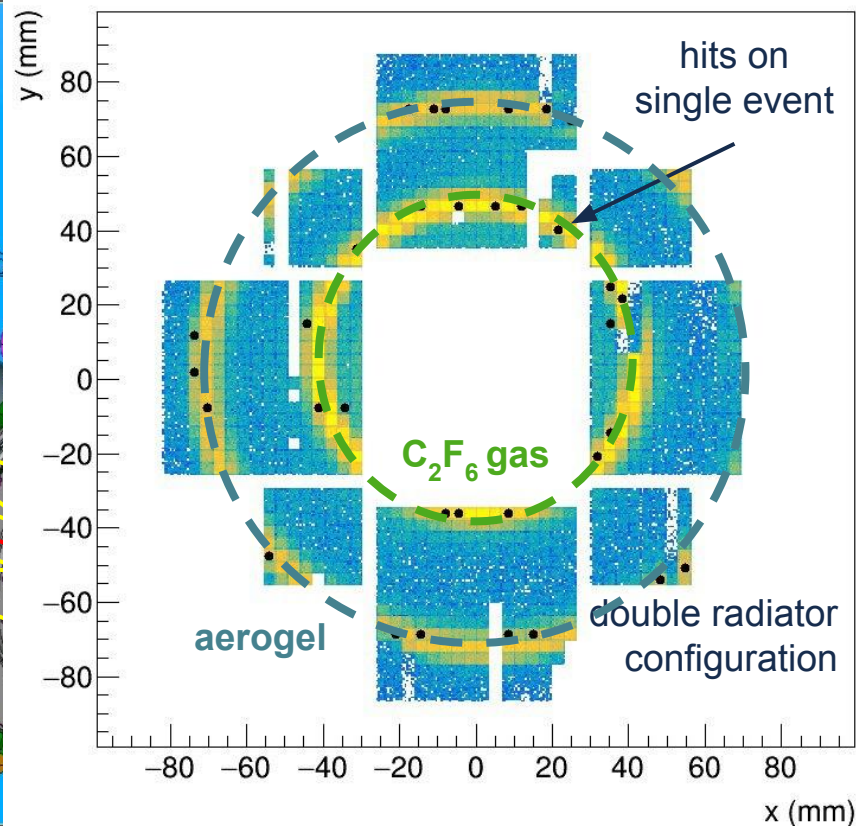
Beam test



Beam test

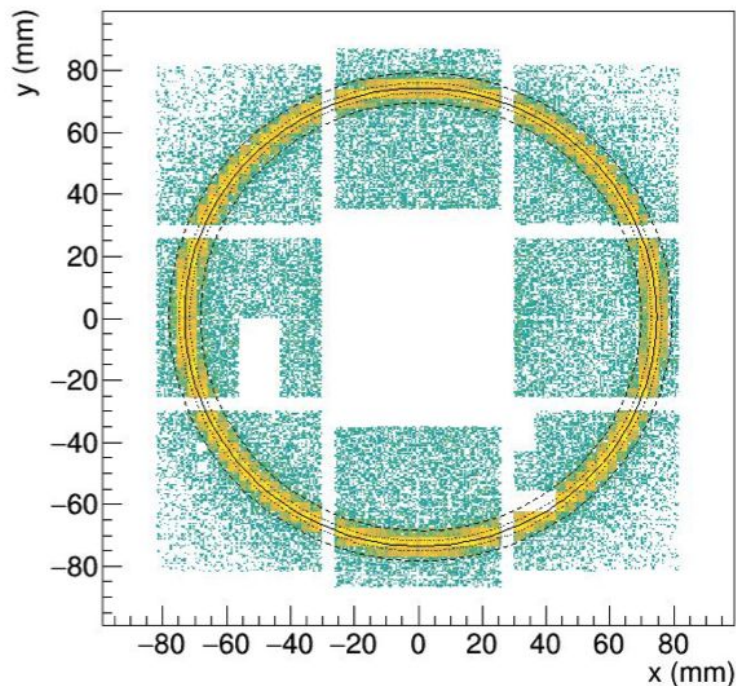


10GeV negative beam



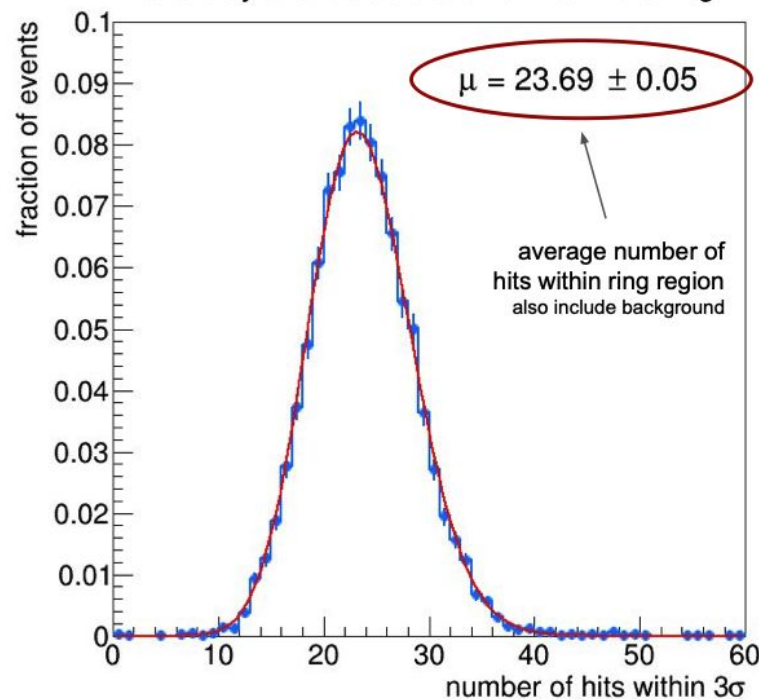
Aerogel

11.5 GeV/c negative beam, $n = 1.02$ aerogel (accumulated events)



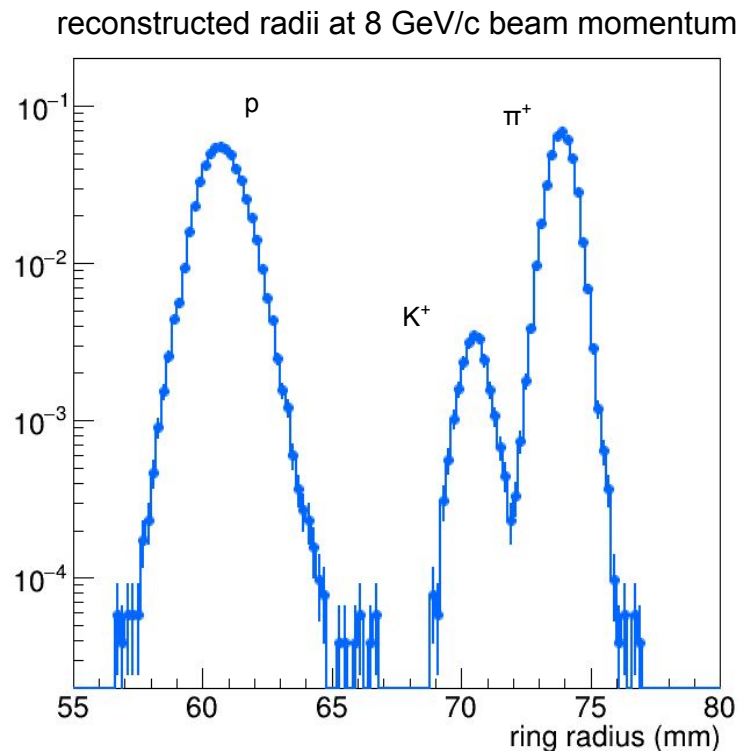
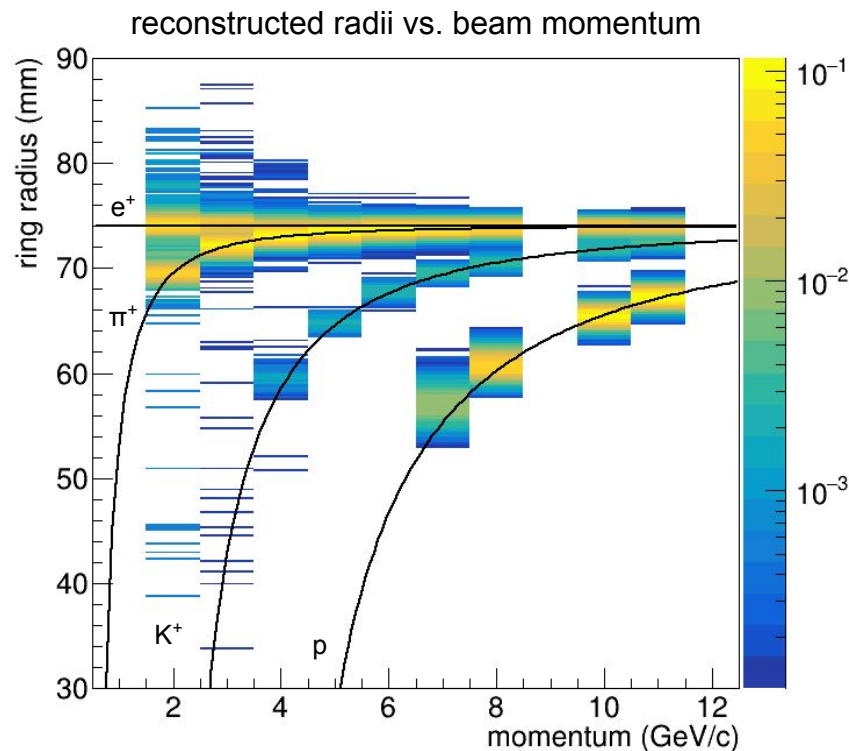
2D fit to accumulated data with realistic model (ring + background)

event-by-event distribution of hits in the ring



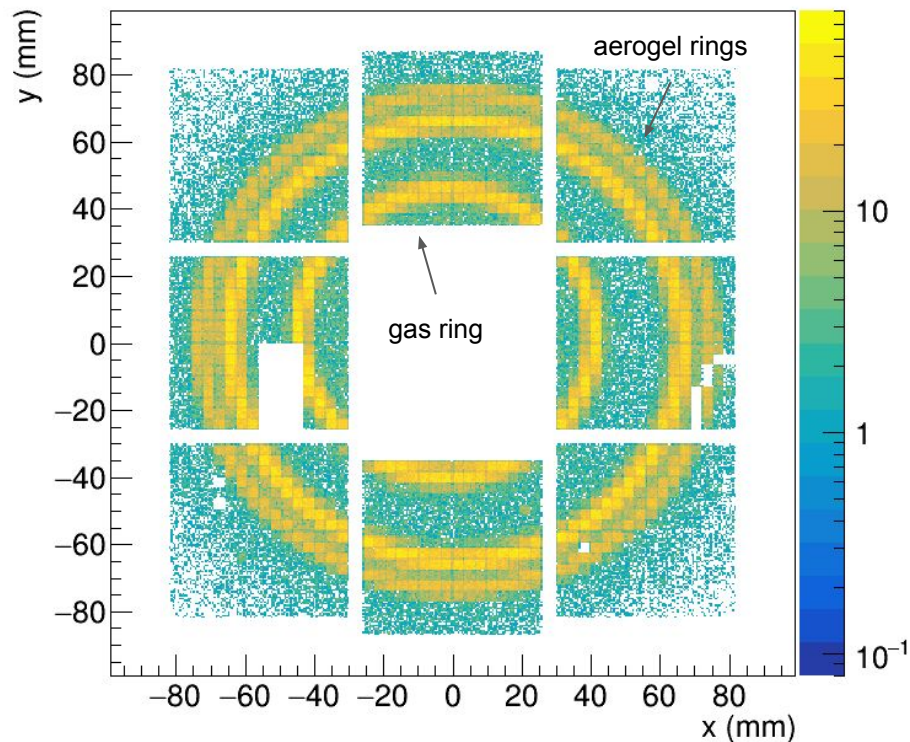
Poisson fit to data, average number of hits is large

Momentum scan

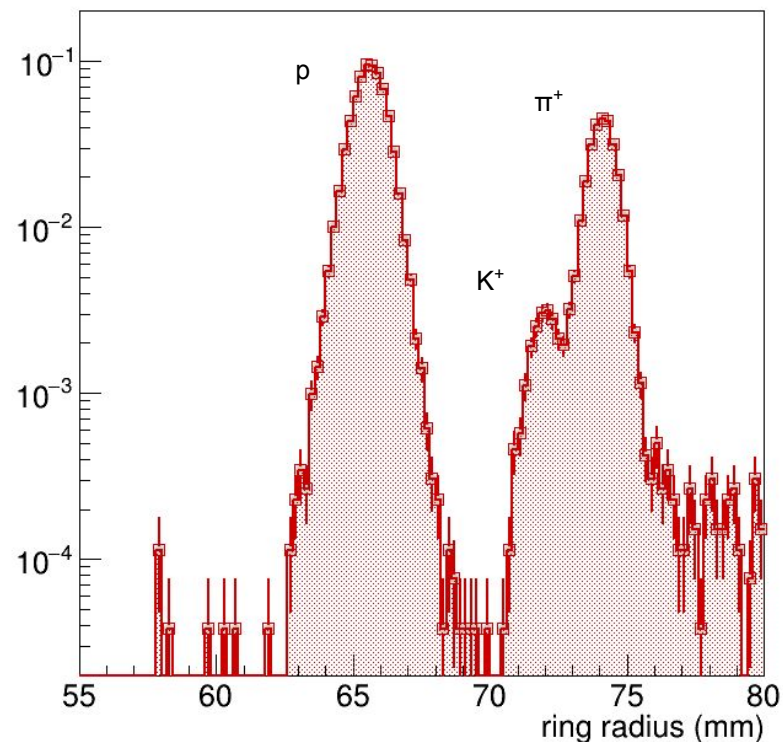


PID w/ Gas & Aerogel

10 GeV/c positive beam with no selection applied

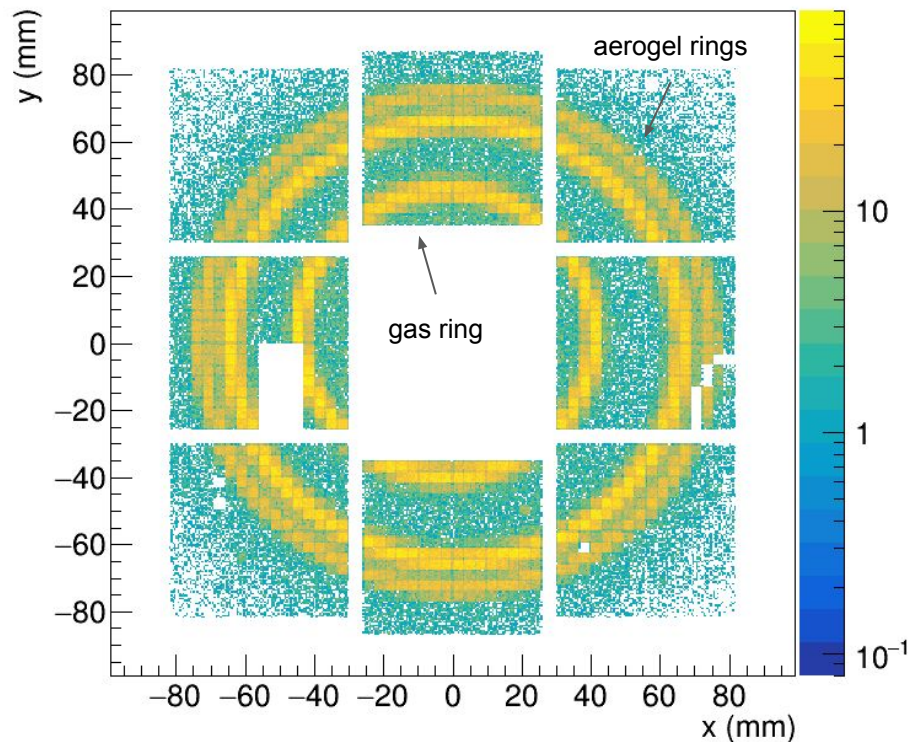


reconstructed radii at 10 GeV/c with no selection applied

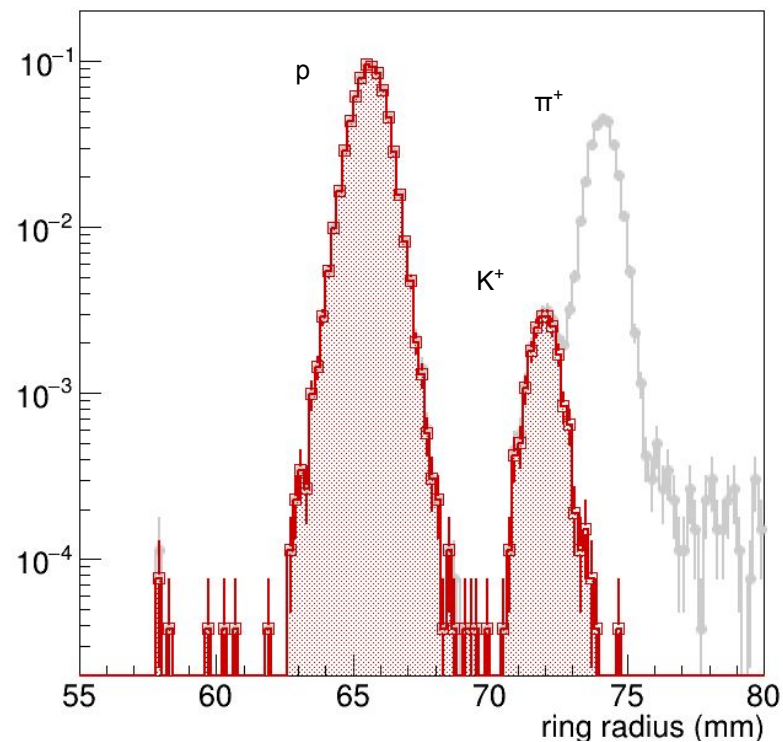


PID w/ Gas & Aerogel

10 GeV/c positive beam with no selection applied

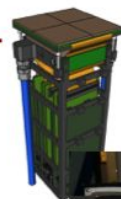


reconstructed radii at 10 GeV/c with gas veto applied





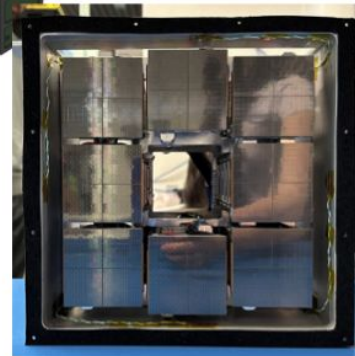
2022
electronics v1



2023
electronics v2

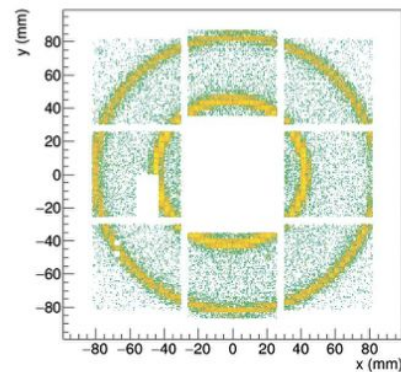
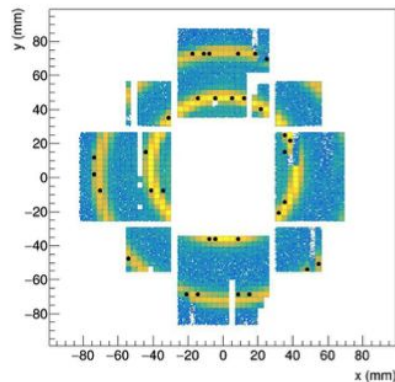
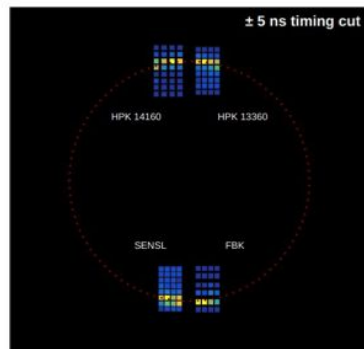


2024
electronics v2.1



towards construction

2025
electronics v3
final prototype



Summary

SiPMs meet dRICH requirements

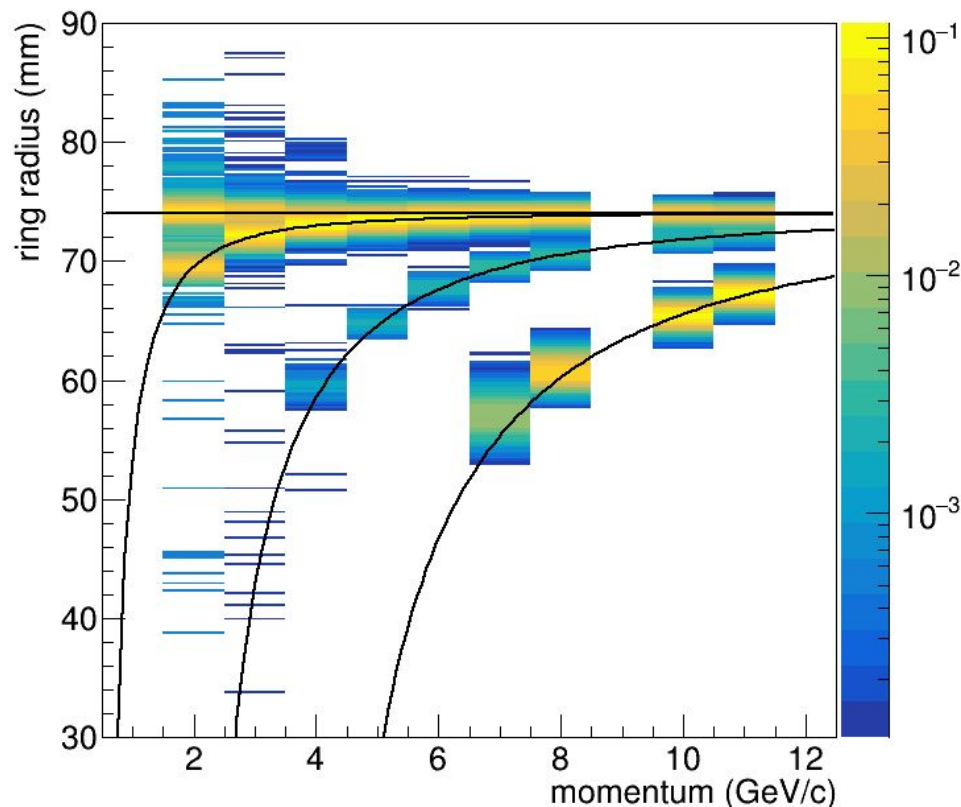
- excellent timing + efficiency, B insensitive

Technical solutions for SiPMs rad damage

- in-situ annealing provides sensors lifetime extension to experiment lifetime

Full readout chain of SiPMs

- We tested full readout chain based on ALCOR w/ multiple successful beam tests



Thank you!

Back-up

The SHIM option and neutron fluence for dRICH sensors

Cons

1. **High dark count rate at room temperature**
2. **High radiation sensitivity**

What can be done?

1. **Cooling** can lower DCR of a factor ~ 2 every $\sim 8^\circ\text{C}$
2. **Timing** can discard background
3. **Annealing** can recover DCR resulted from radiation damage

$10^9 n_{\text{eq}}/\text{cm}^2$ fluence:

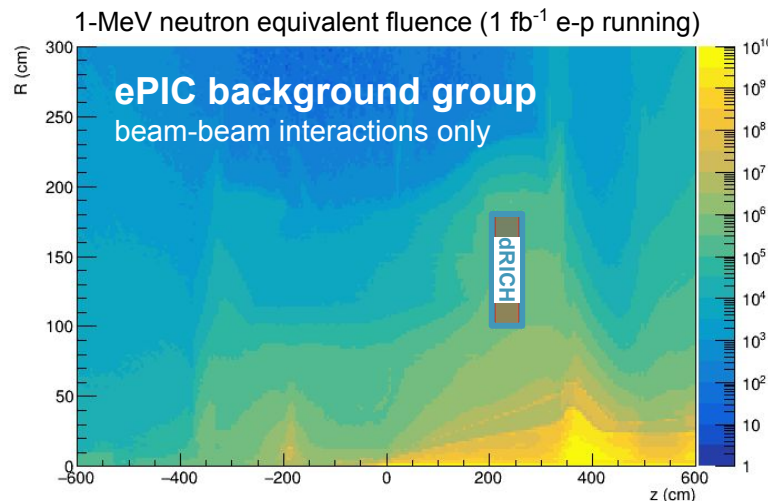
Requirement for the key physics goals is 10 fb^{-1} per center of mass energy and polarization setting

$10^{10} n_{\text{eq}}/\text{cm}^2$ fluence:

Requirement for the nucleon imaging programme is 100 fb^{-1} per center of mass energy and polarization setting

$10^{11} n_{\text{eq}}/\text{cm}^2$ fluence:

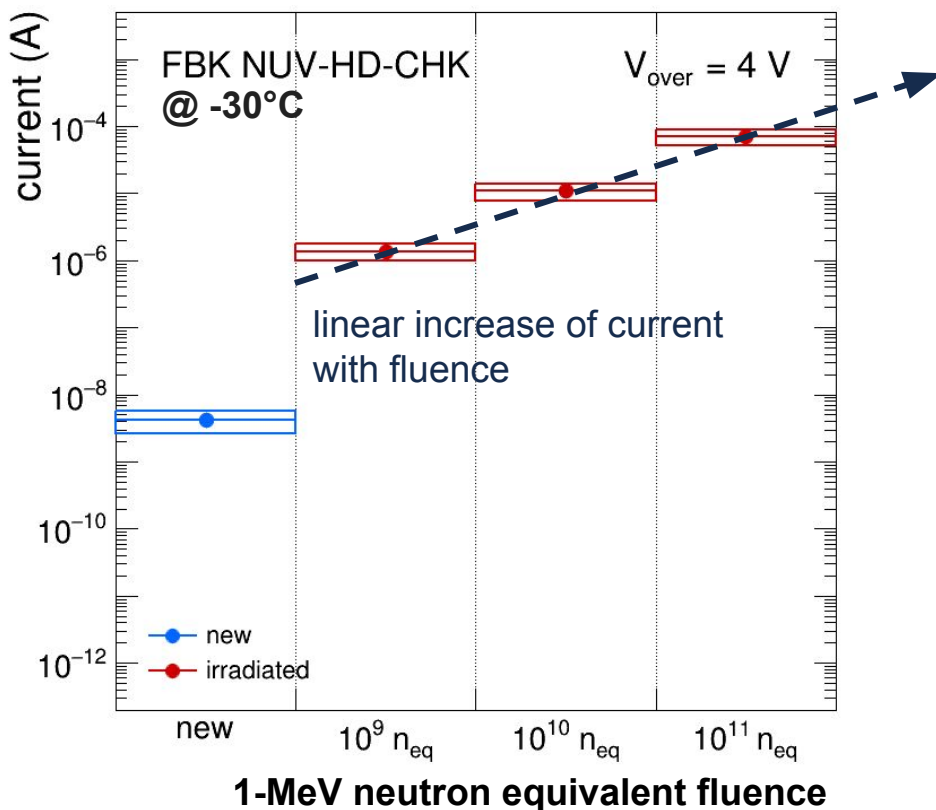
Expected fluence over 10-12 years of operation, might never be reached



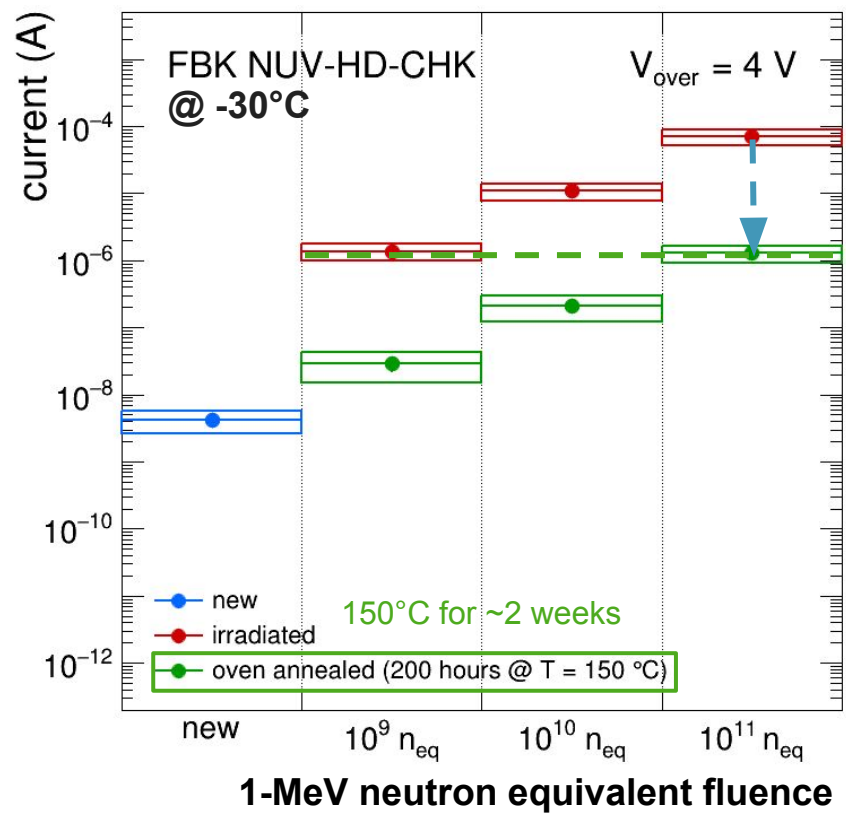
Expected fluence:

average: $\sim 4 \cdot 10^5 n_{\text{eq}}/\text{cm}^2 \text{ fb}^{-1}$
 maximum: $\sim 10^6 n_{\text{eq}}/\text{cm}^2 \text{ fb}^{-1}$
 assumed: $\sim 10^7 n_{\text{eq}}/\text{cm}^2 \text{ fb}^{-1}$
 x10 safety factor

Radiation damage of SiPMs with protons at TIFPA

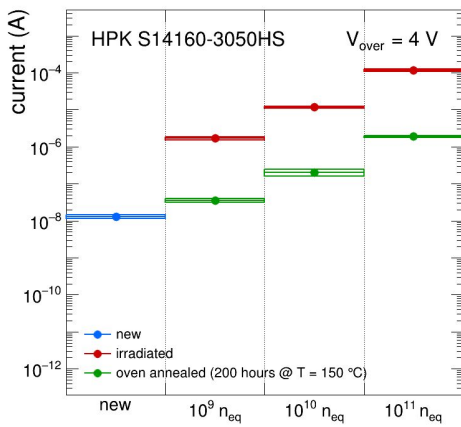
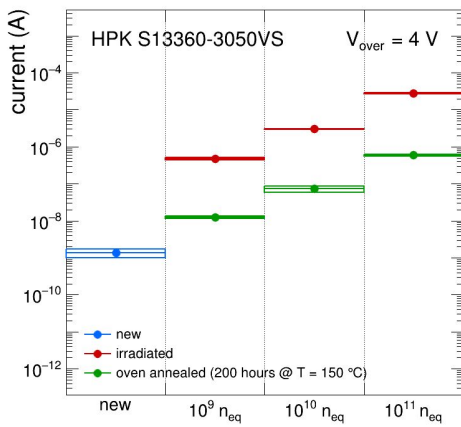
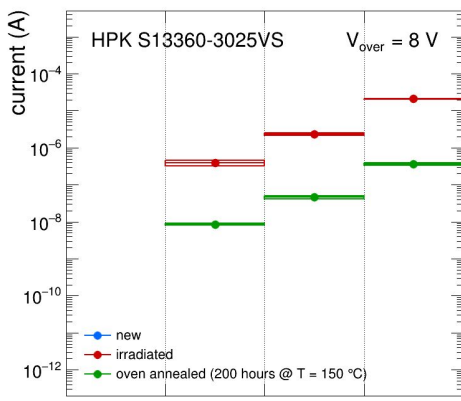


annealing



Offline annealing done with sensors in oven

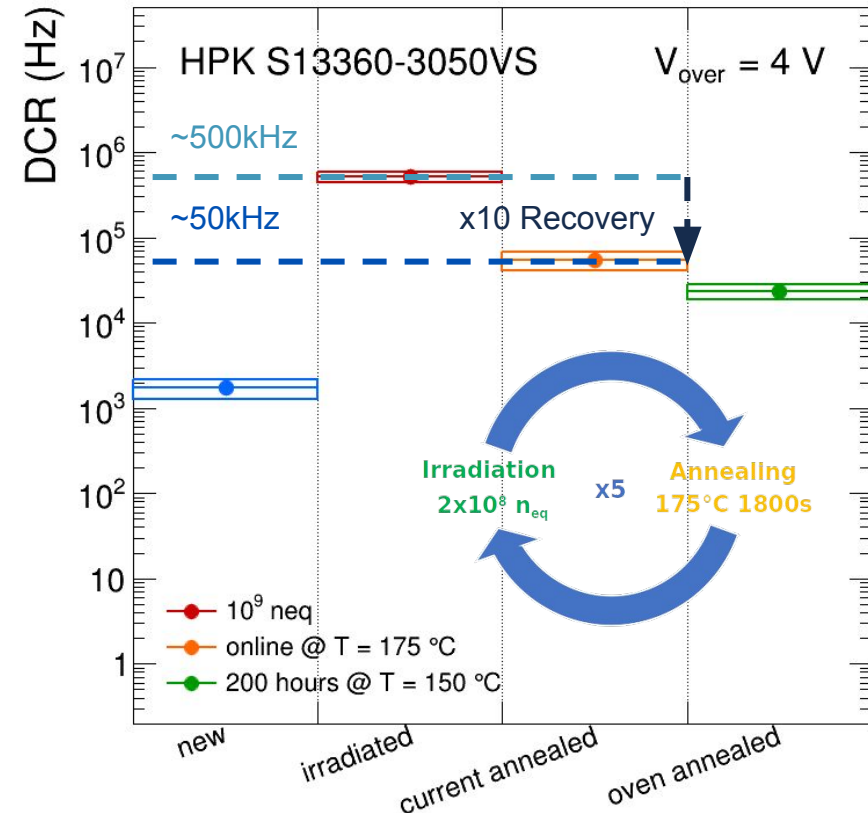
Hamamatsu sensors show very similar behaviours





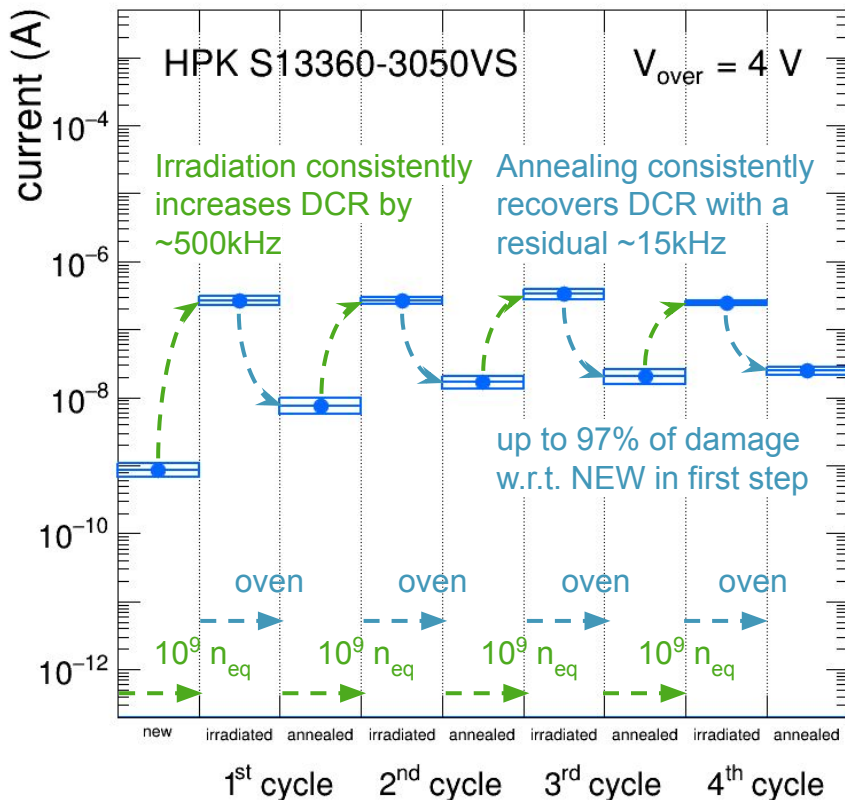
Online annealing done with sensor
in forward bias, delivering
 $\sim 1\text{W/sensor}$

Exposure to radiation is interleaved with annealing cycles as could be the case in the experiment

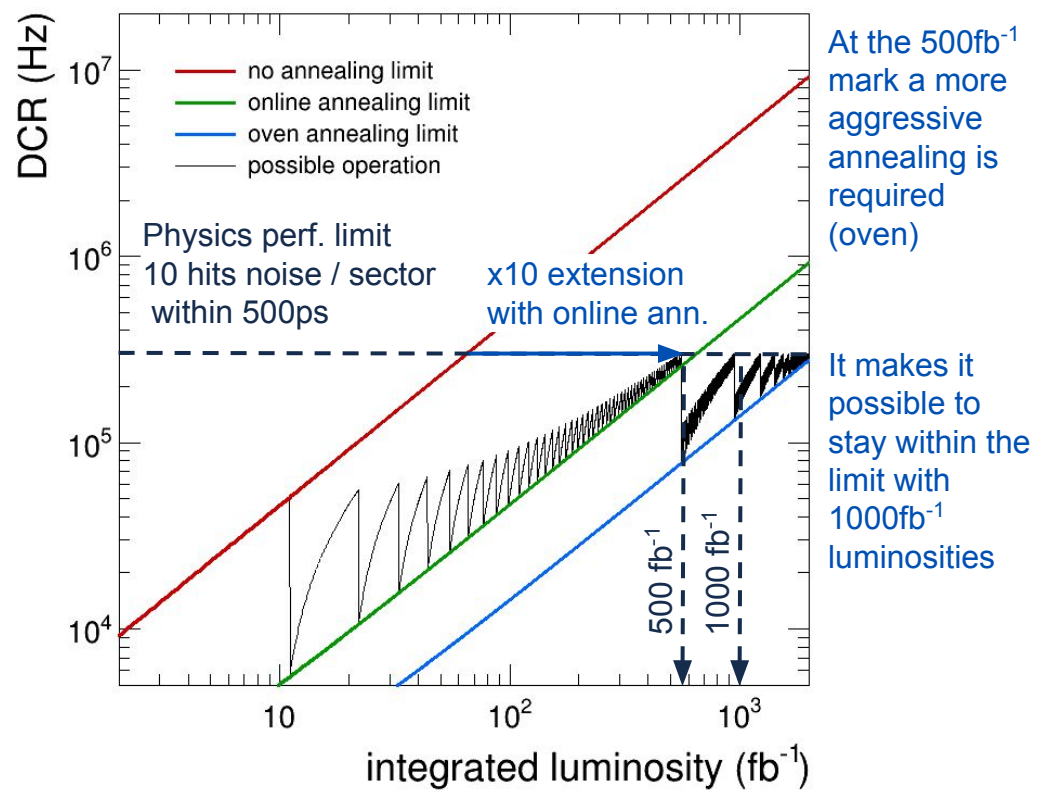
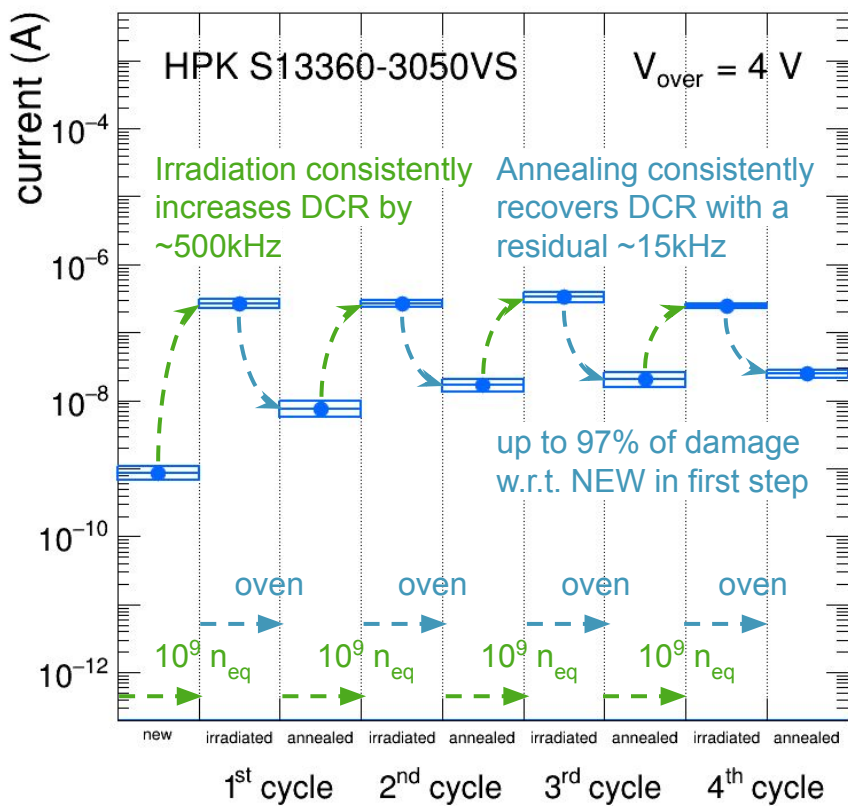


RICH25

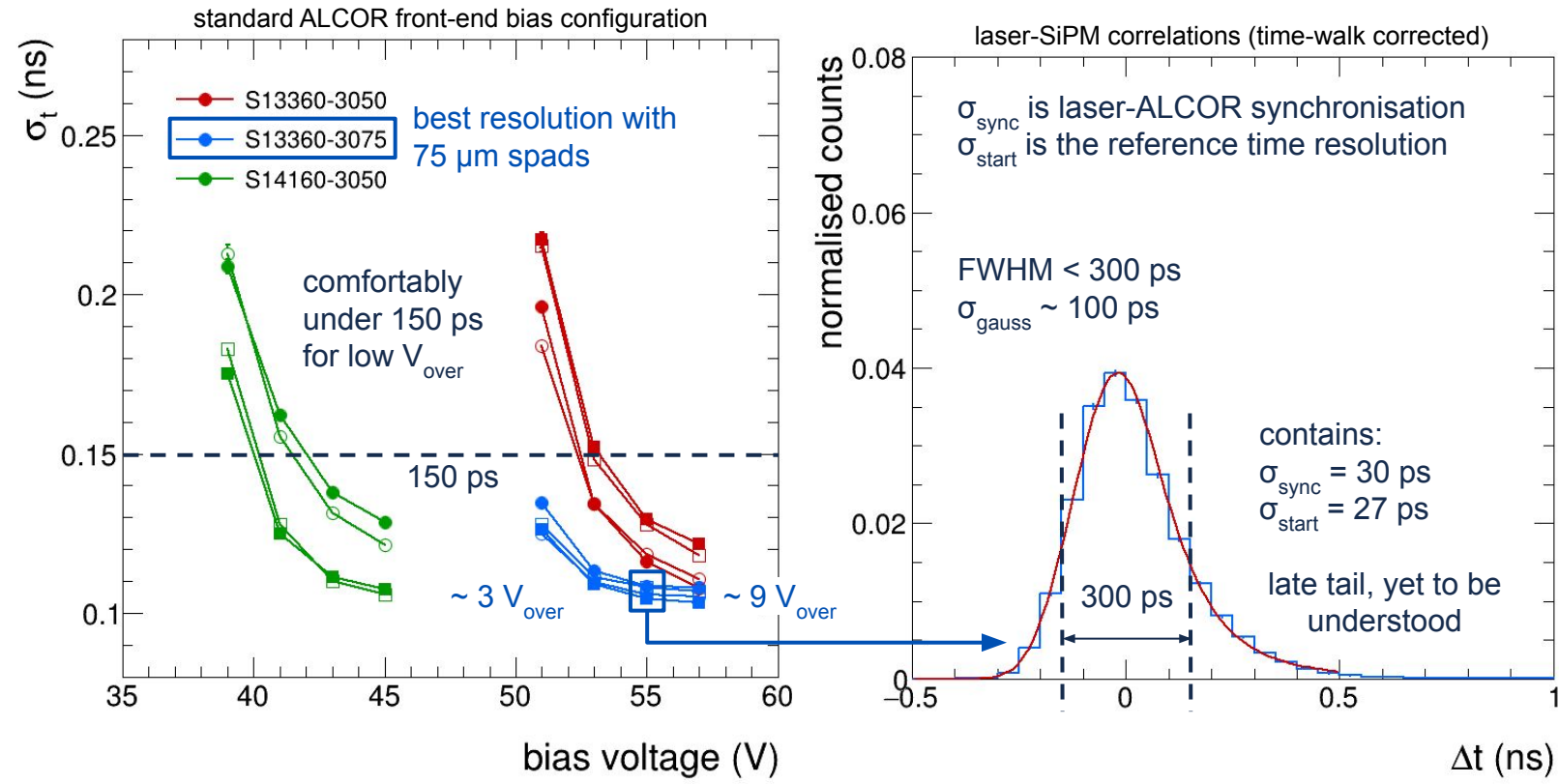
Damage recovery of SiPMs with multiple annealing cycles



Damage recovery of SiPMs with multiple annealing cycles



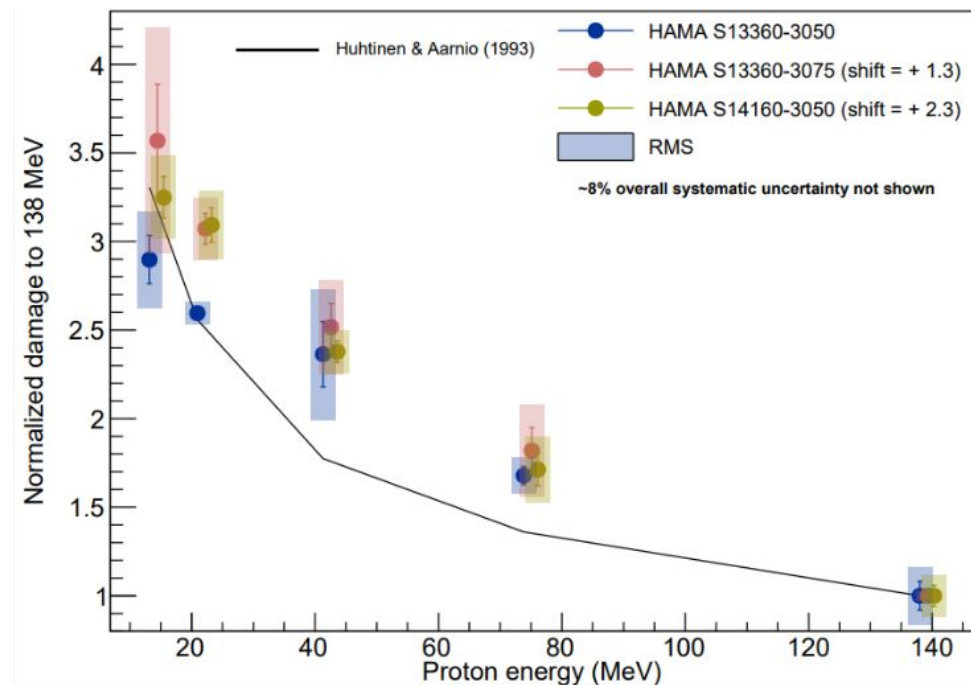
Laser timing w/ ALCOR



p-irr: energy scan

We also tested different incident proton energies.
The theoretical calculations refer to pure Silicon.

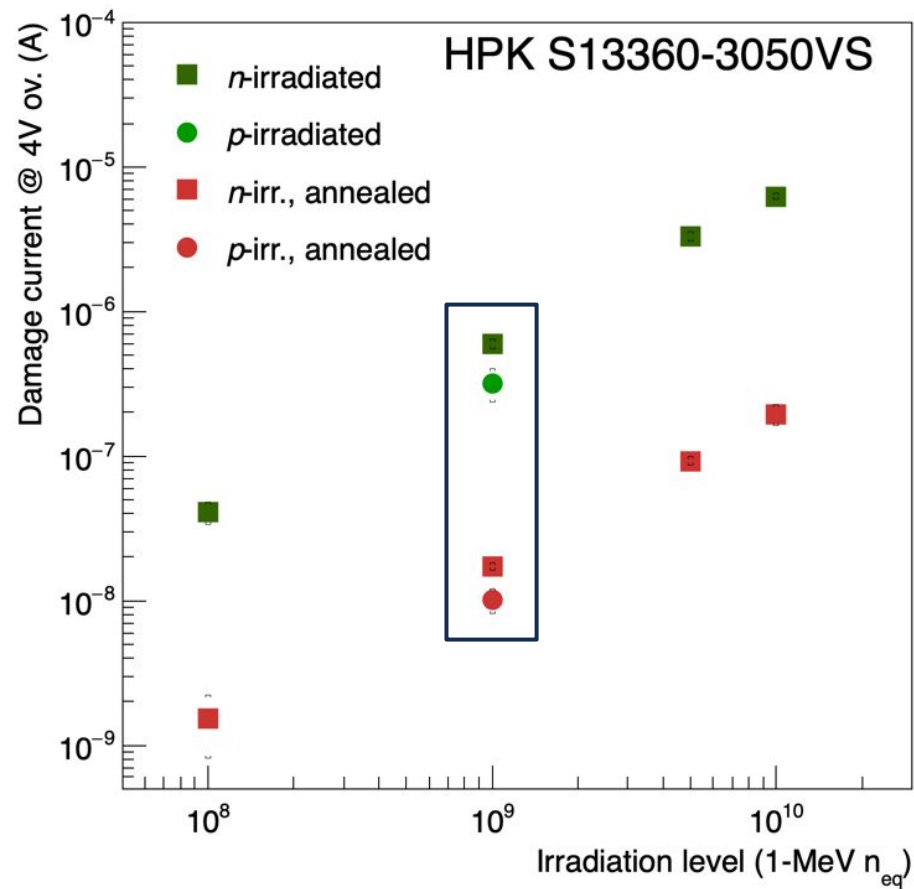
Results are fitting nicely theoretical predictions within few tens of percent



n-irr: fluence scan

We covered a large range of different fluences with the *n*-irradiation. The most puzzling result was a factor 2 difference between *p*-irr and *n*-irr results, in violation of NIEL hypothesis.

Puzzling factor 2 w.r.t. to *p*-irradiation

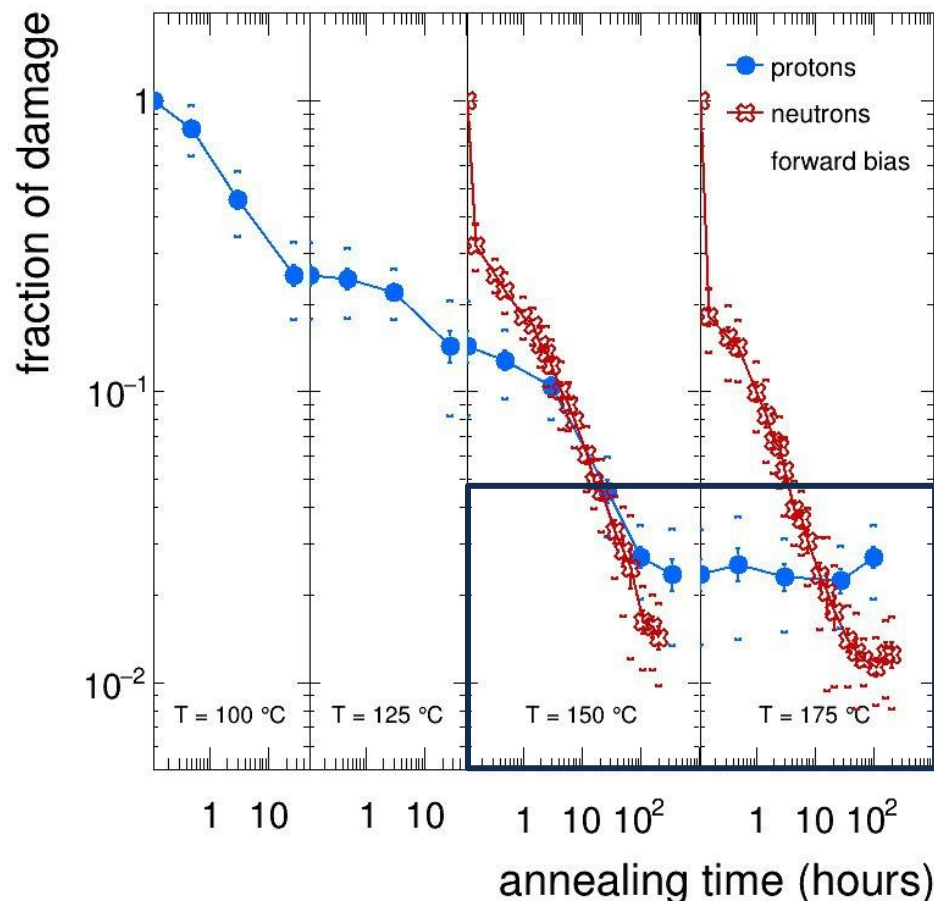


n-irr: forward annealing

We focused on fwd annealing for the *n*-irradiated boards at two different temperatures.

There seem to be a more significant recovery, that is due to the factor 2 in damage w.r.t. *p*-irradiated boards.

p- and *n*-irr. sensors show similar behaviours to annealing

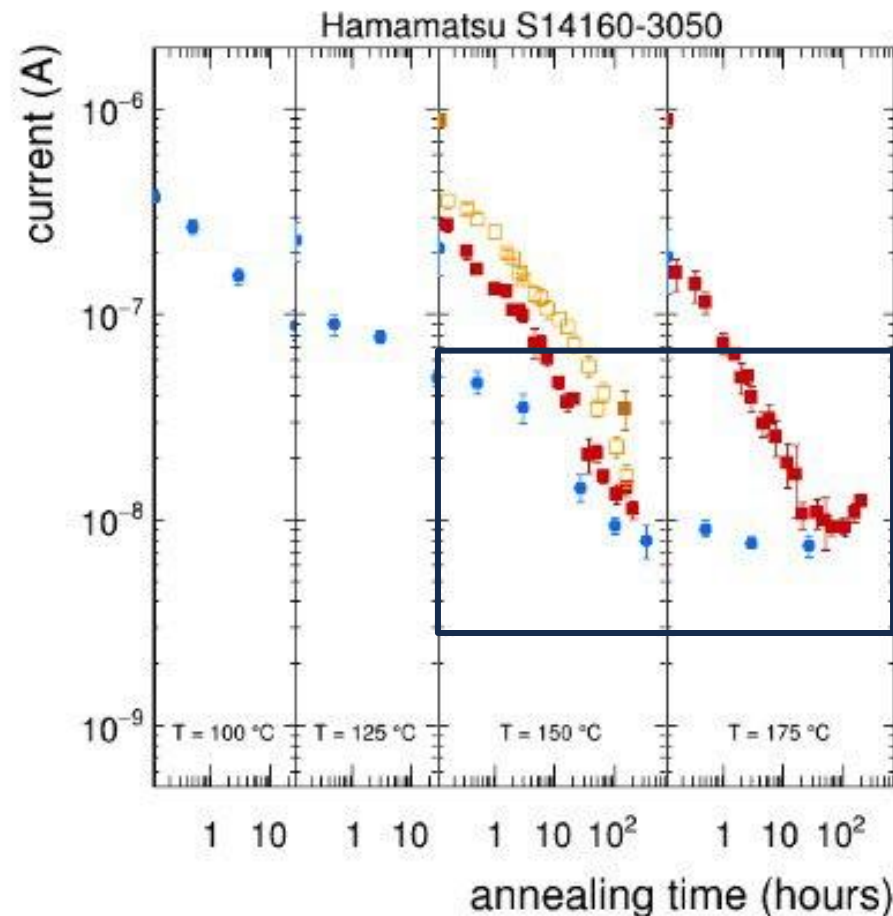


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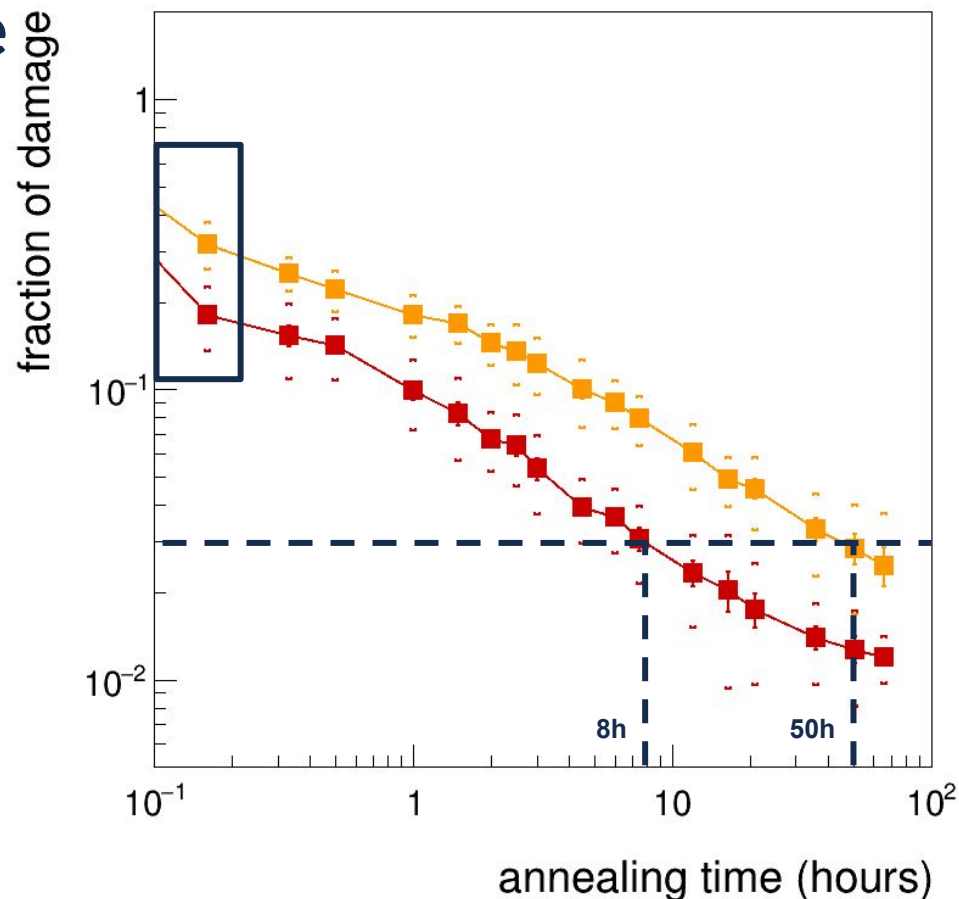


n-irr: annealing temperature

Directly comparing **150C** and **175C** in forward annealing we see that we have an initial decrease that is proportional to the ann. temperature.

Moreover the speed of recovery is also greatly enhanced with a relatively small increase in ann. temperature.

We reach the same cure level, but faster with higher temperatures. (*)

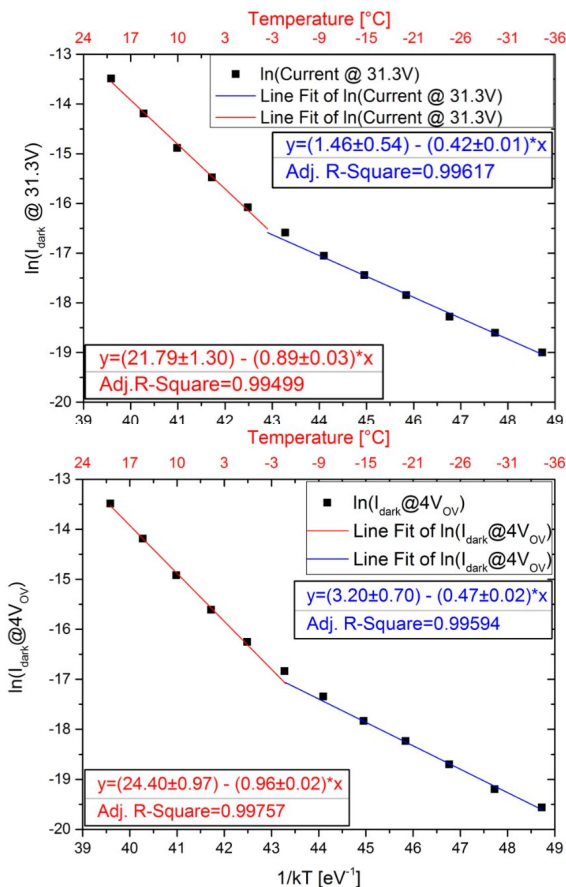
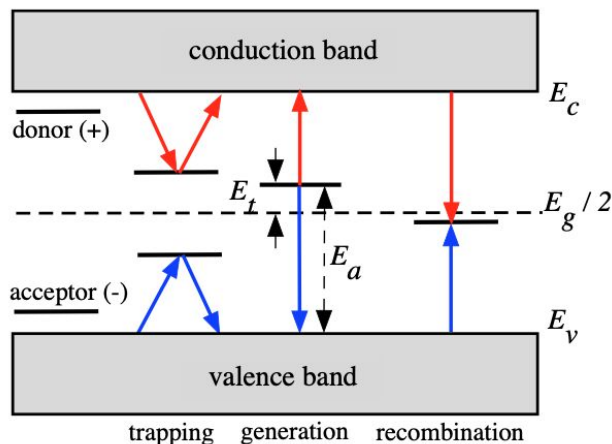


Activation energy

Activation energy can be measured with Arrhenius plots, DCR as a function of temperature at a given overvoltage or at a fixed voltages. The linear dependence of the dark current (log) dictates the activation energy and the dominant process for DCR generation:

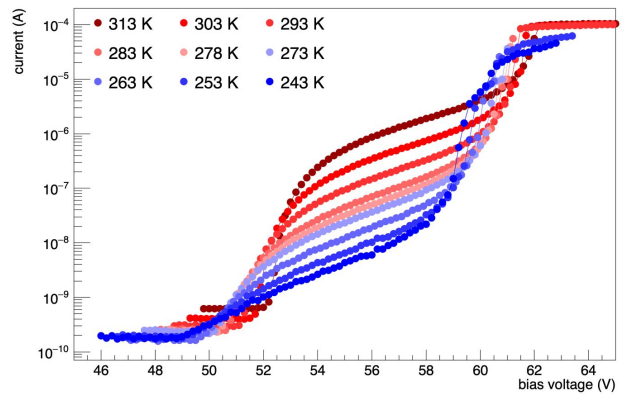
high temperature:
thermal generation

low temperature:
trap assisted generation



Activation energy

We measured the activation energy with the overvoltage method.



Results follow the expectations of a decrease of the act. en. in irr. sensors and an increase with annealing

